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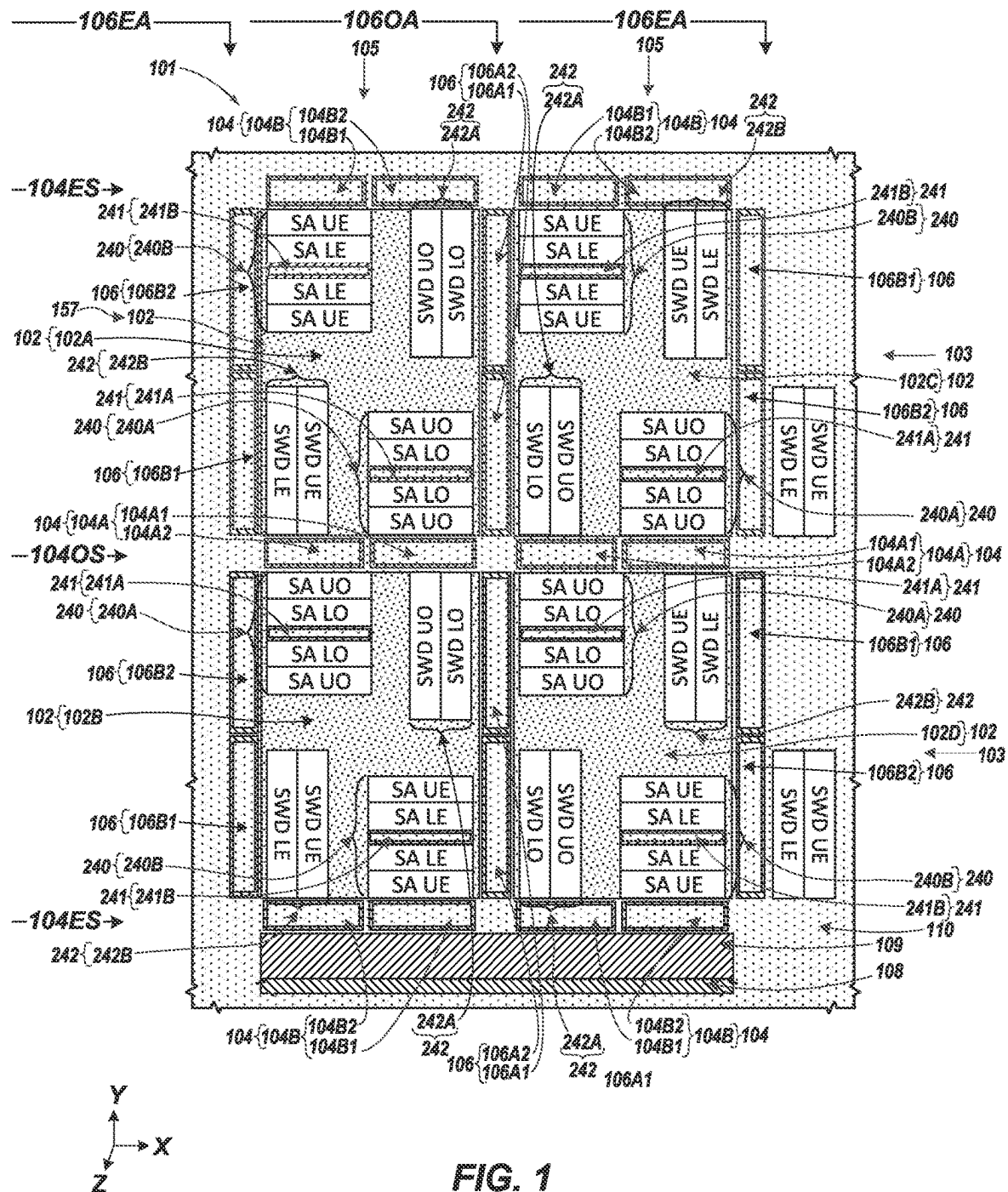
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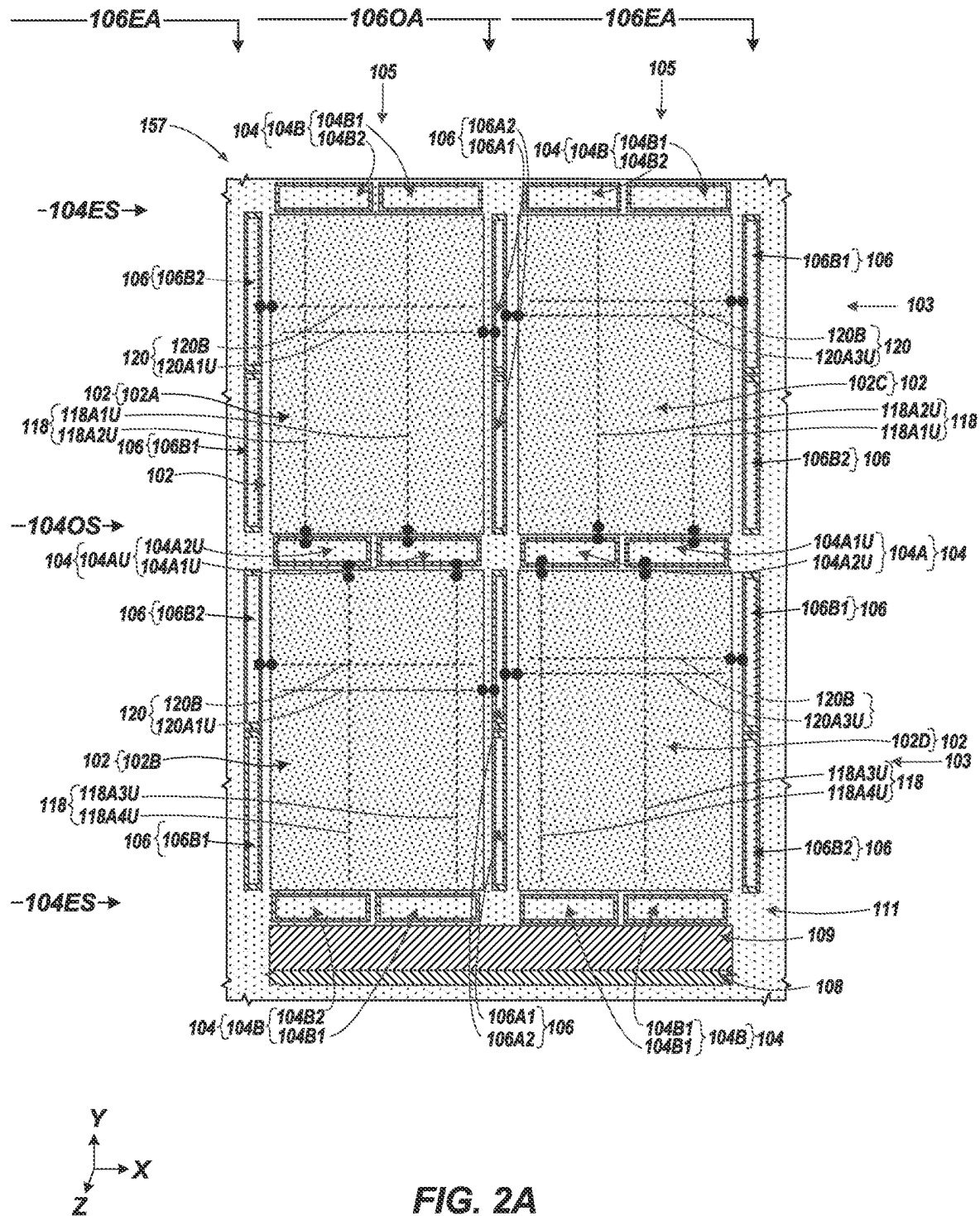
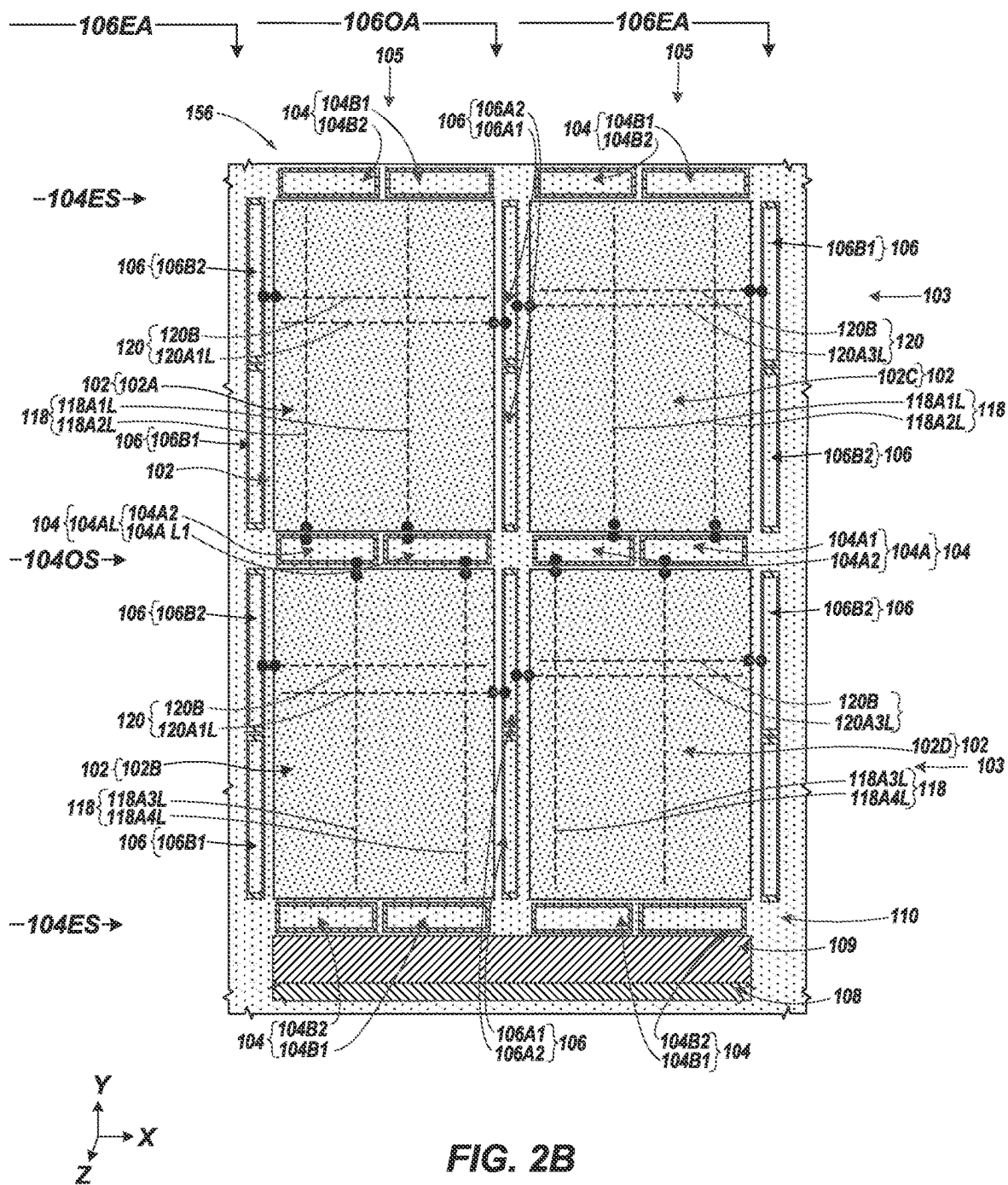
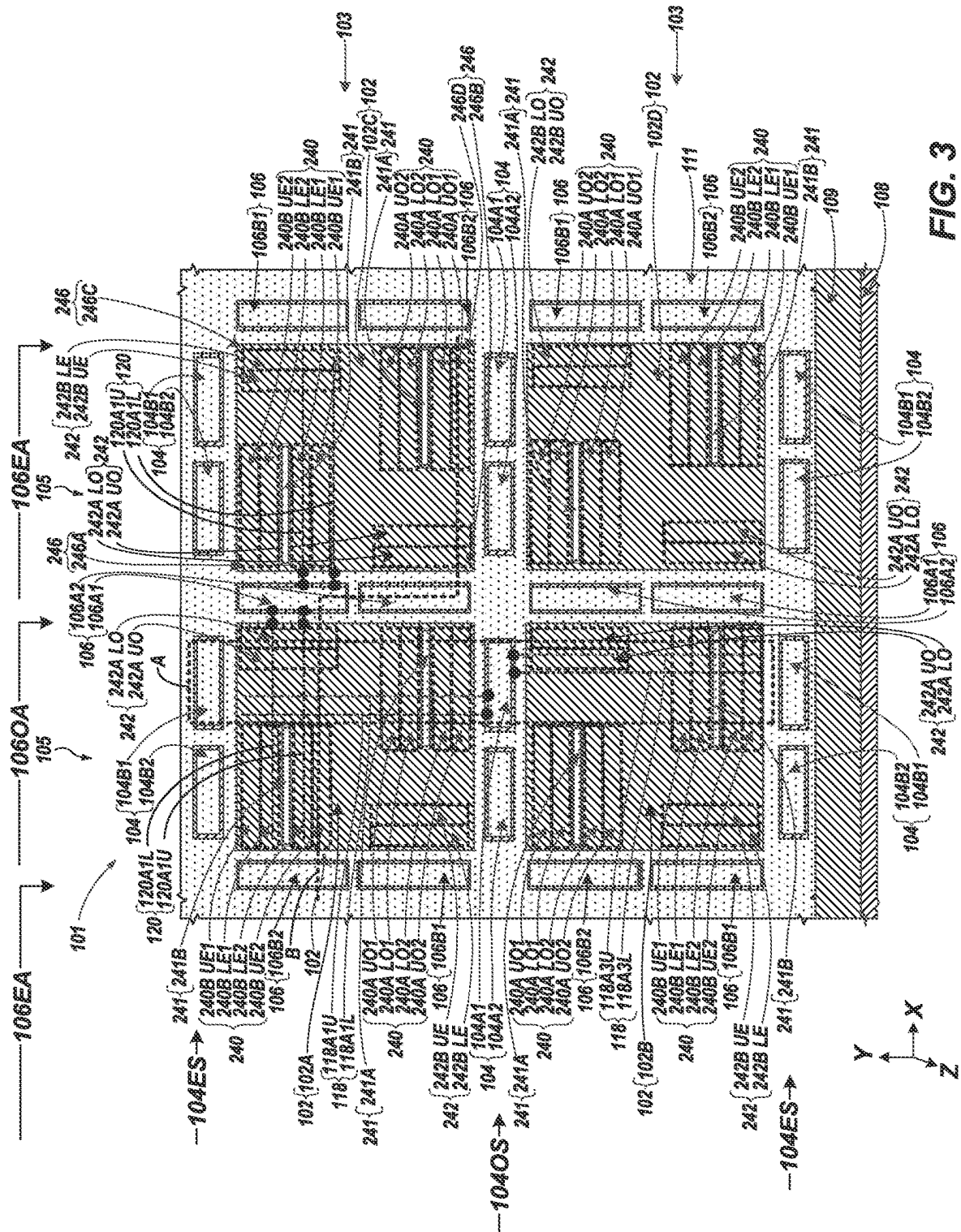
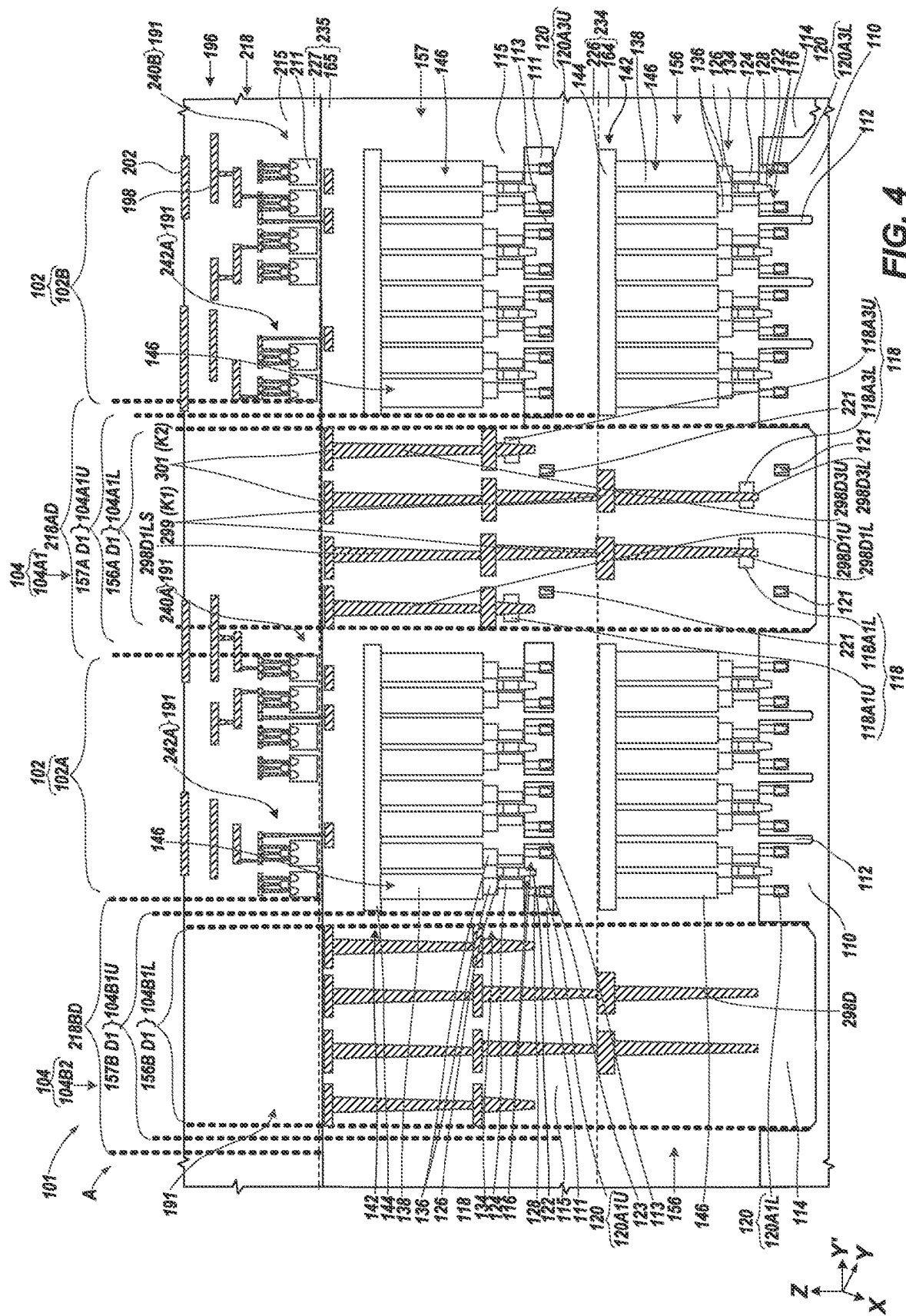


FIG. 2A







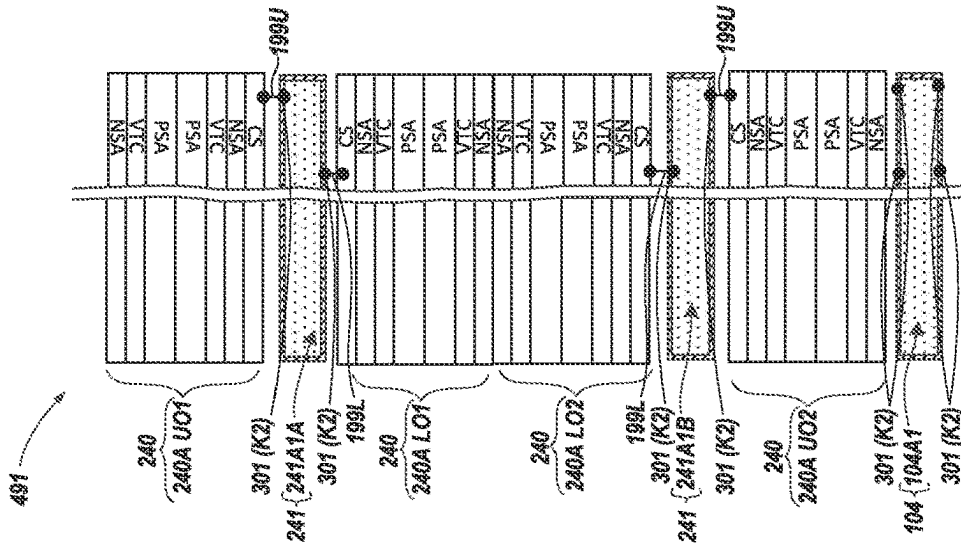


FIG. 5

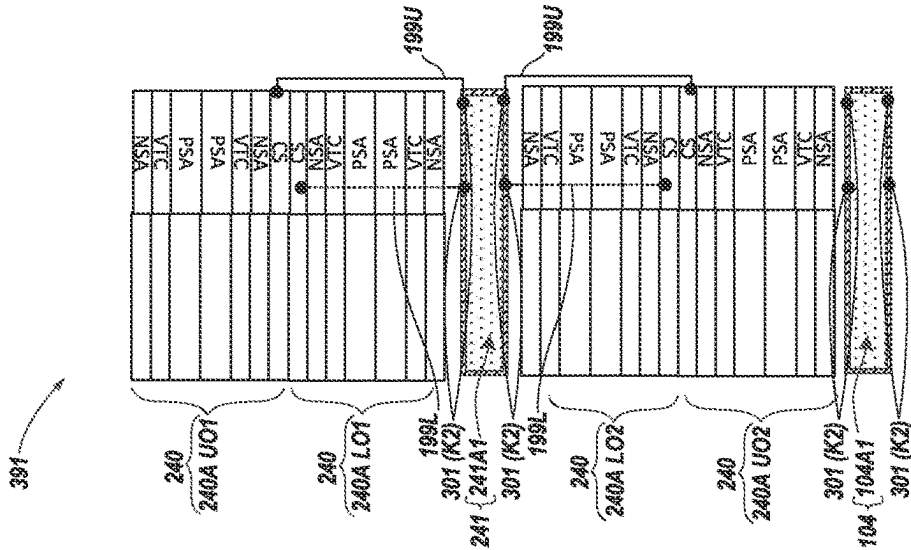


FIG. 6

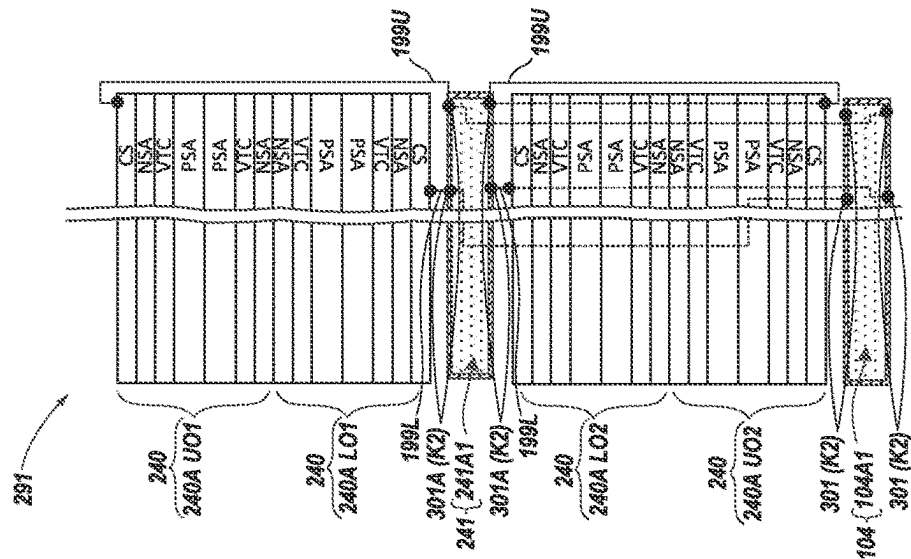
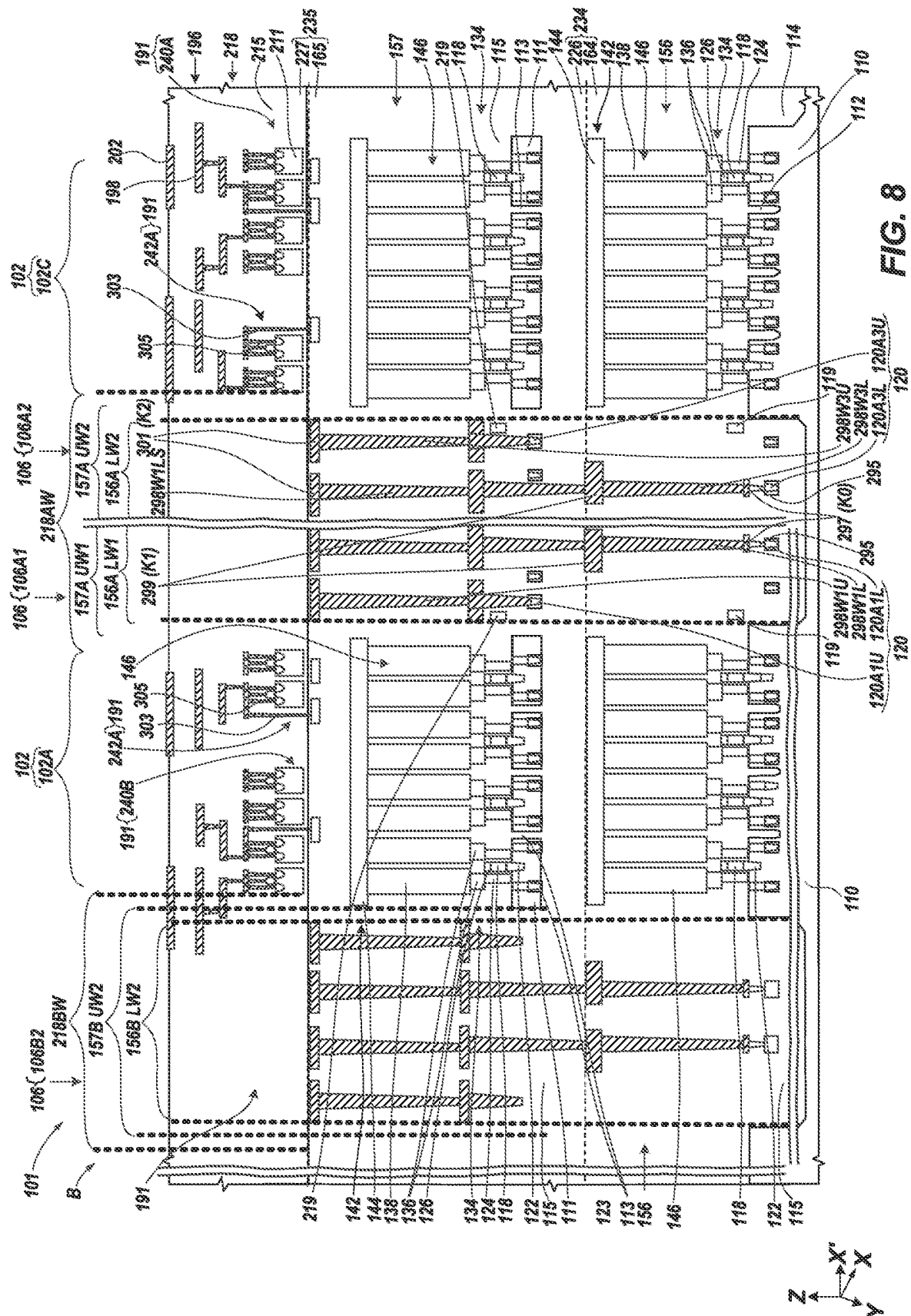
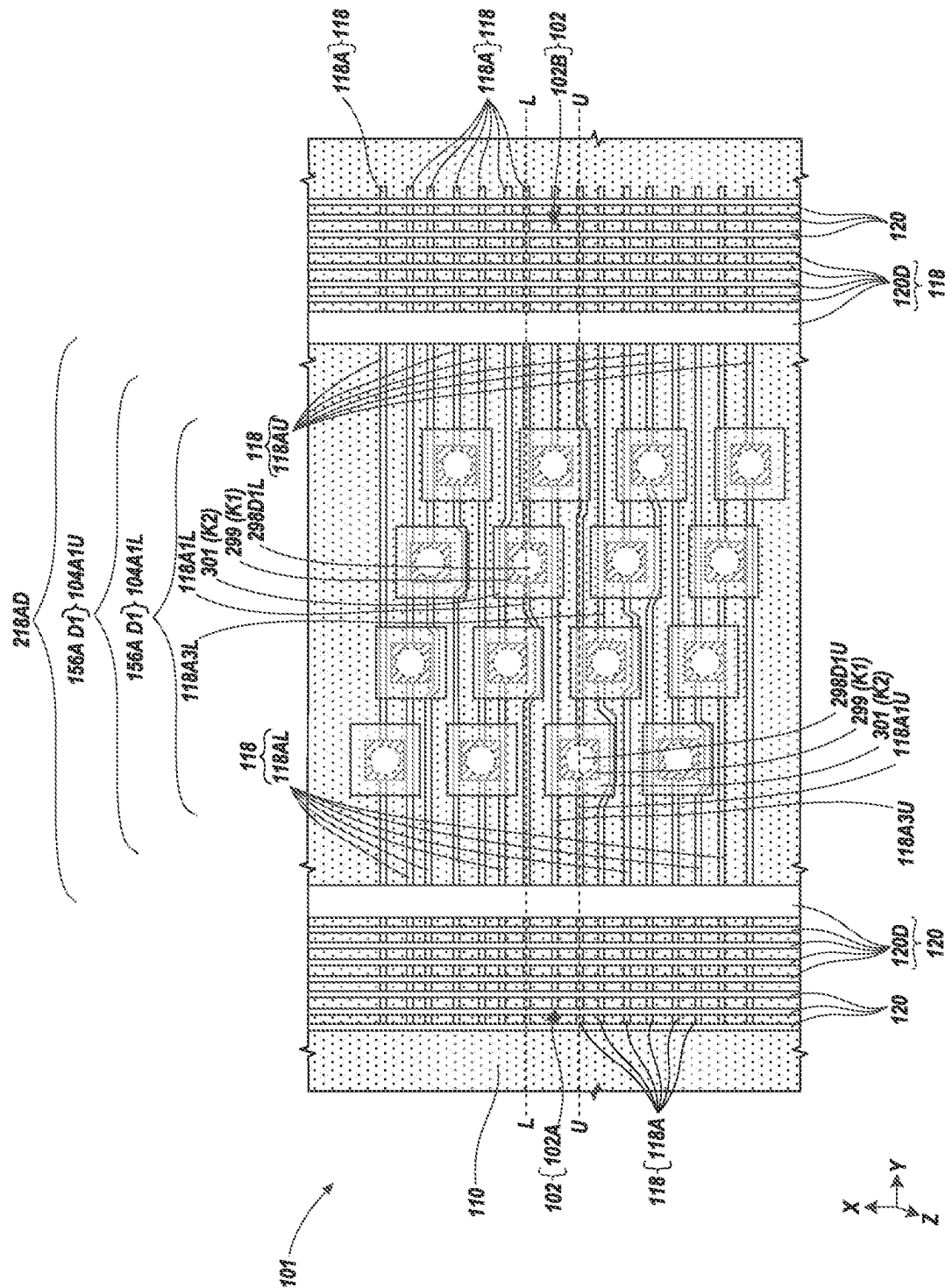
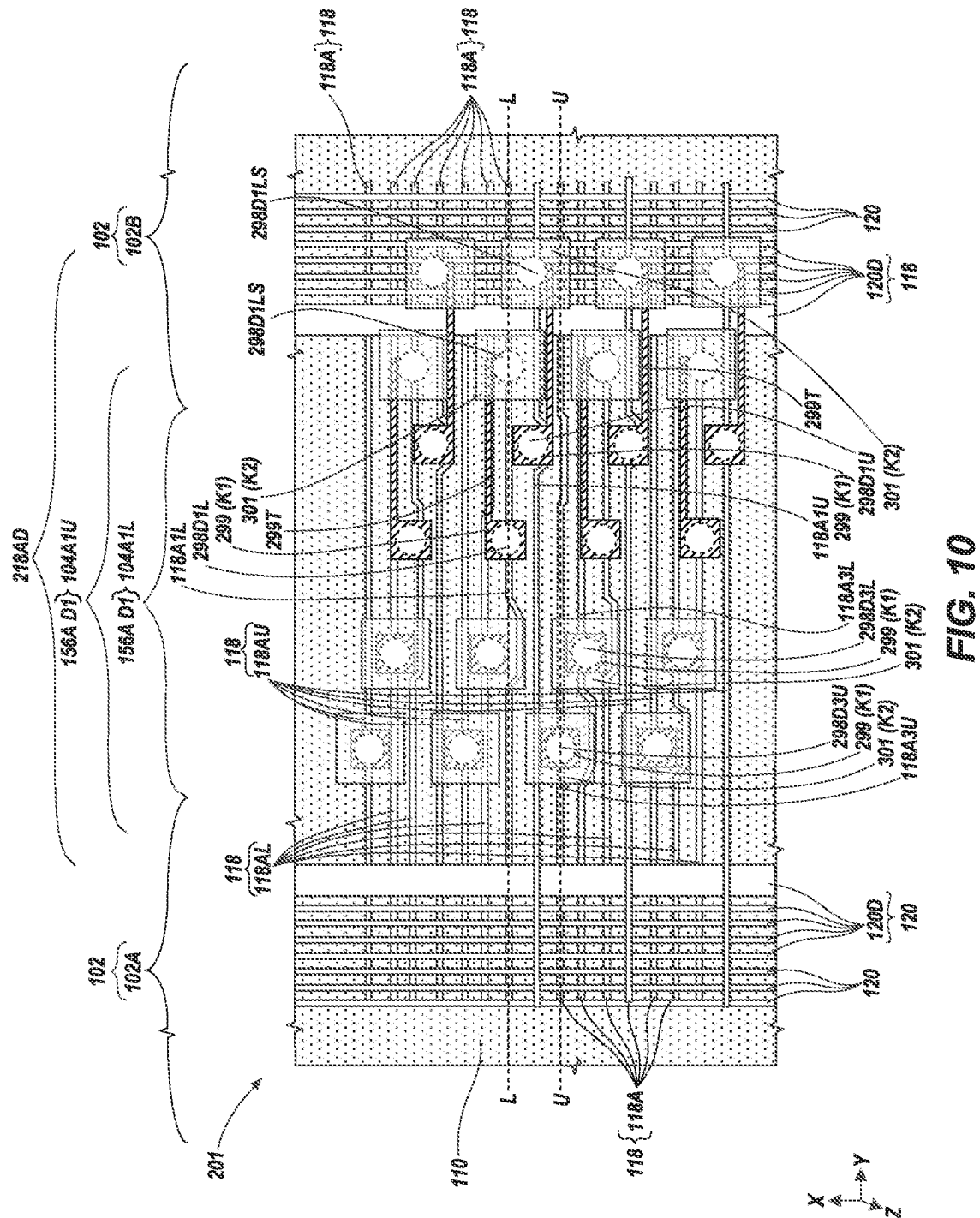


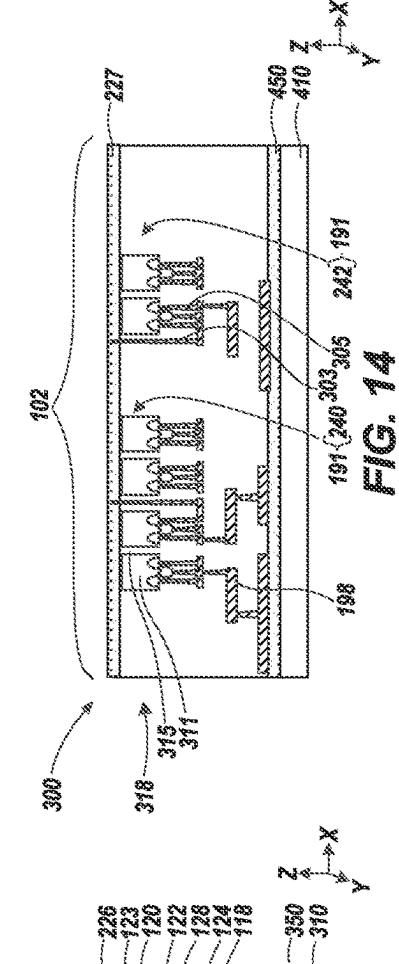
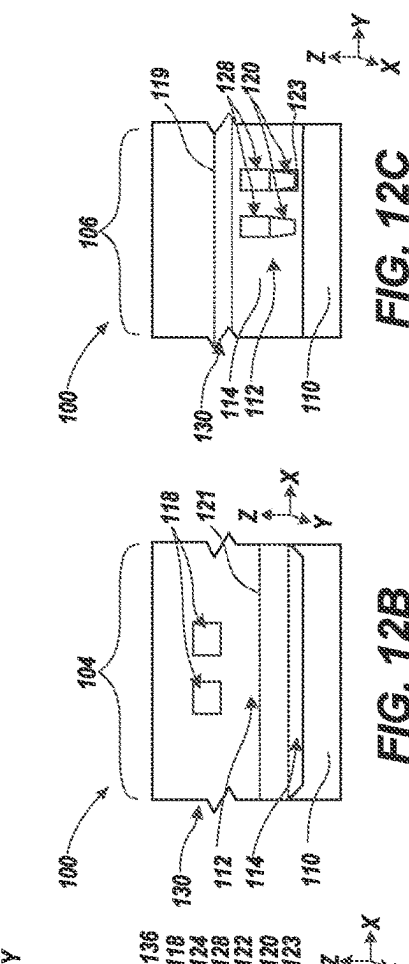
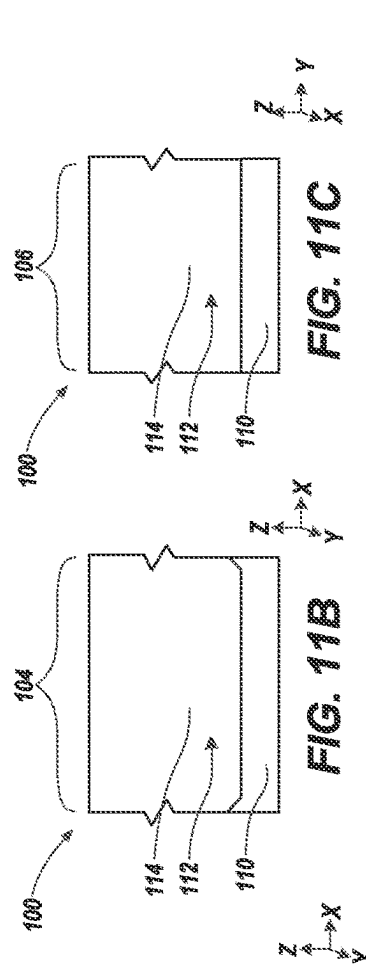
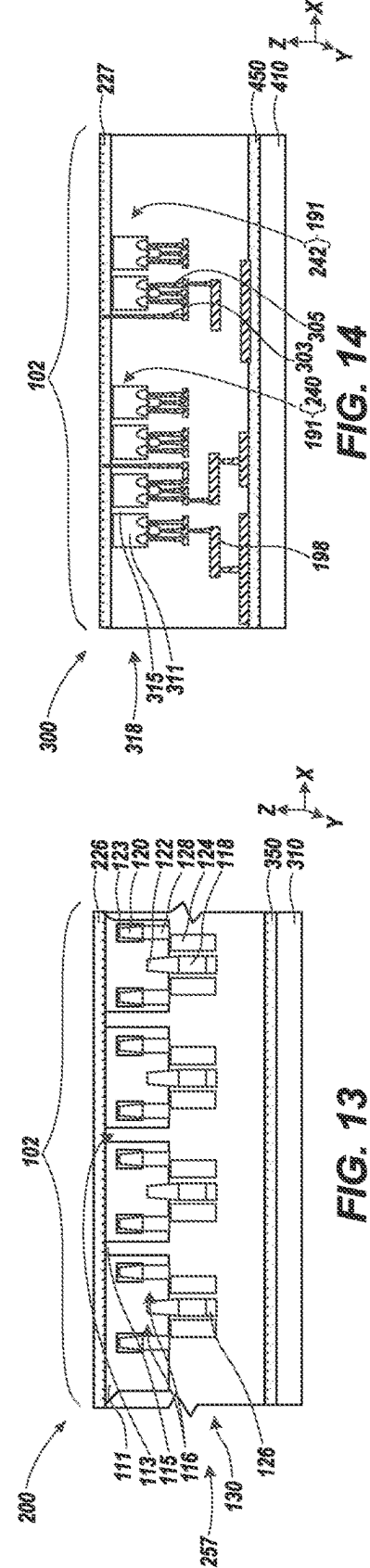
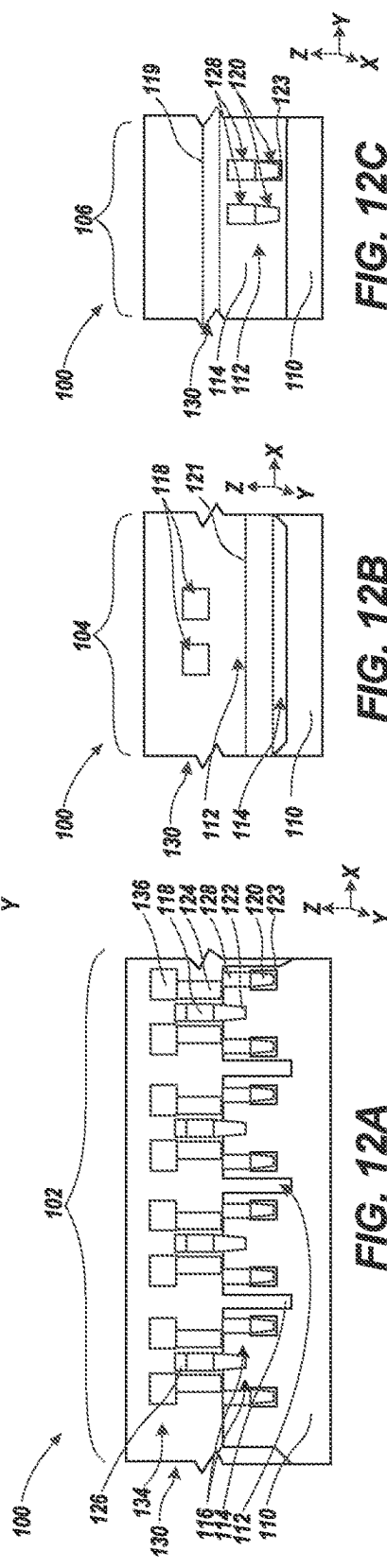
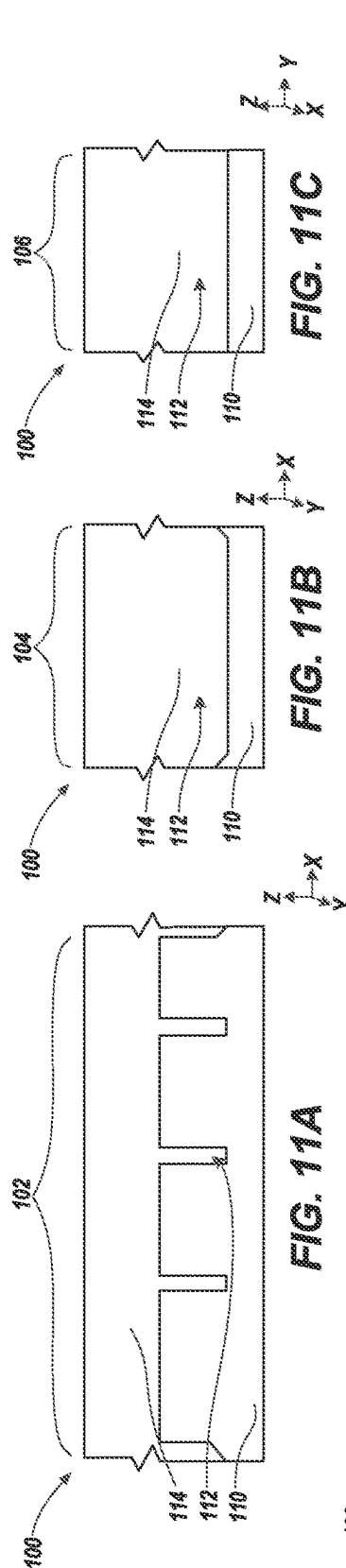
FIG. 7

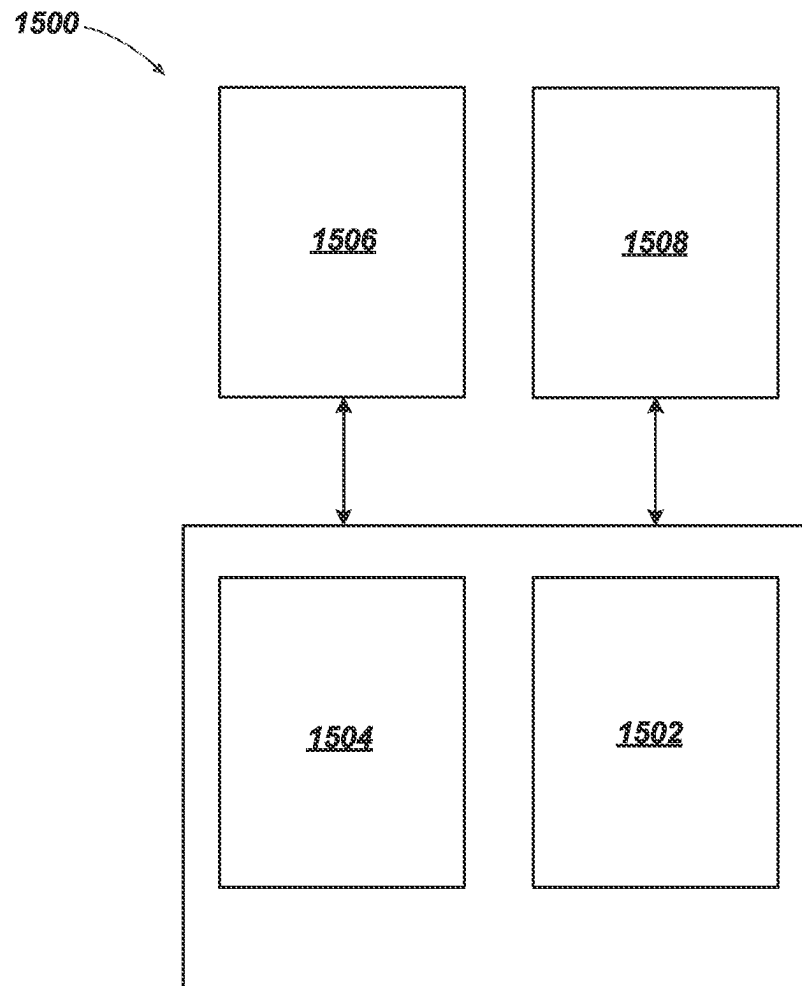




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**FIG. 15**

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METHODS OF FORMING MICROELECTRONIC DEVICES, AND RELATED MICROELECTRONIC DEVICES AND ELECTRONIC SYSTEMS

TECHNICAL FIELD

The disclosure, in various embodiments, relates generally to the field of microelectronic device design. More specifically, the disclosure relates microelectronic devices including control logic circuitry overlying memory arrays, and to related memory devices, and electronic systems.

BACKGROUND

Microelectronic devices often have complex signal routing that may affect performance. One example of a microelectronic device is a memory device. Memory devices are generally provided as internal integrated circuits in computers or other electronic devices. There are many types of memory devices including, but not limited to, volatile memory devices. One type of volatile memory device is a dynamic random access memory (DRAM) device. A DRAM device may include a memory array including DRAM cells arranged in rows extending in a first horizontal direction and columns extending in a second horizontal direction. In one design configuration, an individual DRAM cell includes an access device (e.g., a transistor) and a storage node device (e.g., a capacitor) electrically connected to the access device. The DRAM cells of a DRAM device are electrically accessible through digit lines and word lines arranged along the rows and columns of the memory array and in electrical communication with control logic devices within a base control logic structure of the DRAM device.

Control logic devices within a base control logic structure underlying a memory array of a DRAM device have been used to control operations on the DRAM cells of the DRAM device. Control logic devices of the base control logic structure can be provided in electrical communication with digit lines and word lines coupled to the DRAM cells by way of structures (e.g., vertical routing structures, such as conductive contacts; horizontal routing structures, such as traces). Unfortunately, three-dimensional (3D) memory device (e.g., 3D DRAM device) architectures can require complex and congested routing designs to electrically connect DRAM cells to control logic circuitry, such as sub-word line drivers (SWD) circuitry and sense amplifiers (SA) circuitry.

BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1 is a simplified plan view of a microelectronic device, in accordance with an embodiment of the disclosure.

FIG. 2A is a simplified plan view of an upper array portion of the microelectronic device depicted in FIG. 1.

FIG. 2B is a simplified plan view of a lower array portion of the microelectronic device depicted in FIG. 1.

FIG. 3 is a more detailed plan view of portions of the upper array portion depicted in FIG. 2A, portions of the lower array portion depicted in FIG. 2B, and control logic devices including the control logic devices in the microelectronic device depicted in FIG. 1.

FIG. 4 is a simplified, partial longitudinal cross sectional elevation view of portions of the microelectronic device depicted in FIGS. 1, 2A, 2B, and 3.

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FIG. 5 is a simplified top plan view of portions of a sense amplifier device assembly in the control logic circuitry depicted in FIGS. 1, 3, and 4.

FIG. 6 is a simplified top plan view of portions of a sense amplifier device assembly in the control logic circuitry depicted in FIGS. 1, 3, and 4.

FIG. 7 is a simplified top plan view of portions of a sense amplifier assembly in control logic circuitry depicted in FIGS. 1, 3, and 4.

FIG. 8 is a simplified, partial longitudinal cross sectional elevation view of portions of the microelectronic device depicted in FIGS. 1, 2A, 2B, 3, and 4.

FIG. 9 is a simplified plan view of a portion of the microelectronic device including one of the digit line socket regions that projects downwardly into a digit line exit region according to several embodiments.

FIG. 10 is a simplified plan view of a portion of another digit line exit region in another embodiment of a microelectronic device, where distribution of some electrical interconnects between digit lines and sense amplifiers are arranged in a halfway distributed configuration.

FIGS. 11A through 11C are simplified, partial longitudinal cross-sectional views of an array region (FIG. 11A), a digit line exit region (FIG. 11B), and a word line exit region (FIG. 11C), and a socket region (FIG. 2D) of the microelectronic device structure shown in FIG. 1 at the processing stage assembling a memory array device.

FIGS. 12A through 12C are simplified, partial longitudinal cross-sectional views of the array region (FIG. 12A), the digit line exit region (FIG. 12B), and the word line exit region (FIG. 12C) shown in FIGS. 11A through 11C, respectively, at another processing stage of the method of forming the microelectronic device following the processing stage of FIGS. 11A through 11C.

FIG. 13 illustrates a simplified, partial longitudinal cross-sectional view of the array region (FIG. 12A) at a processing stage of the method of forming the microelectronic device following the processing stage of FIGS. 12A through 12C, in accordance with embodiments of the disclosure. FIG. 14 illustrates a simplified, partial longitudinal cross-sectional view of the array region (FIG. 12A) at a processing stage of the method of forming the microelectronic device following the processing stage of FIGS. 12A through 12C, in accordance with additional embodiments of the disclosure.

FIG. 15 is a block diagram of an electronic system, according to embodiments of the disclosure.

DETAILED DESCRIPTION

The following description provides specific details, such as material compositions, shapes, and sizes, in order to provide a thorough description of embodiments of the disclosure. However, a person of ordinary skill in the art would understand that the embodiments of the disclosure may be practiced without employing these specific details. Indeed, the embodiments of the disclosure may be practiced in conjunction with conventional microelectronic device fabrication techniques employed in the industry. In addition, the description provided below does not form a complete process flow for manufacturing a microelectronic device (e.g., a memory device). The structures described below do not form a complete microelectronic device. Only those process acts and structures necessary to understand the embodiments of the disclosure are described in detail below. Additional acts to form a complete microelectronic device from the structures may be performed by conventional fabrication techniques.

Drawings presented herein are for illustrative purposes only, and are not meant to be actual views of any particular material, component, structure, device, or system. Variations from the shapes depicted in the drawings as a result, for example, of manufacturing techniques and/or tolerances, are to be expected. Thus, embodiments described herein are not to be construed as being limited to the particular shapes or regions as illustrated, but include deviations in shapes that result, for example, from manufacturing. For example, a region illustrated or described as box-shaped may have rough and/or nonlinear features, and a region illustrated or described as round or curved may include some rough and/or linear features. Moreover, sharp angles that are illustrated may be rounded, and vice versa. Thus, the regions illustrated in the figures are schematic in nature, and their shapes are not intended to illustrate the precise shape of a region and do not limit the scope of the present claims. The drawings are not necessarily to scale. Additionally, elements common between figures may retain the same numerical designation.

As used herein, a “memory device” means and includes microelectronic devices exhibiting memory functionality, but not necessarily limited to memory functionality. Stated another way, and by way of non-limiting example only, the term “memory device” includes not only conventional memory (e.g., conventional volatile memory; conventional non-volatile memory), but also includes an application specific integrated circuit (ASIC) (e.g., a system on a chip (SoC)), a microelectronic device combining logic and memory, and a graphics processing unit (GPU) incorporating memory.

As used herein, the term “configured” refers to a size, shape, material composition, orientation, and arrangement of one or more of at least one structure and at least one apparatus facilitating operation of one or more of the structure and the apparatus in a pre-determined way.

As used herein, the terms “vertical,” “longitudinal,” “horizontal,” and “lateral” are in reference to a major plane of a structure and are not necessarily defined by Earth’s gravitational field. A “horizontal” or “lateral” direction is a direction that is substantially parallel to the major plane of the structure, while a “vertical” or “longitudinal” direction is a direction that is substantially perpendicular to the major plane of the structure. The major plane of the structure is defined by a surface of the structure having a relatively large area compared to other surfaces of the structure. With reference to the figures, a “horizontal” or “lateral” direction may be perpendicular to an indicated “Z” axis, and may be parallel to an indicated “X” axis and/or parallel to an indicated “Y” axis; and a “vertical” or “longitudinal” direction may be parallel to an indicated “Z” axis, may be perpendicular to an indicated “X” axis, and may be perpendicular to an indicated “Y” axis.

As used herein, features (e.g., regions, structures, devices) described as “neighboring” one another means and includes features of the disclosed identity (or identities) that are located most proximate (e.g., closest to) one another. Additional features (e.g., additional regions, additional structures, additional devices) not matching the disclosed identity (or identities) of the “neighboring” features may be disposed between the “neighboring” features. Put another way, the “neighboring” features may be positioned directly adjacent one another, such that no other feature intervenes between the “neighboring” features; or the “neighboring” features may be positioned indirectly adjacent one another, such that at least one feature having an identity other than that associated with at least one the “neighboring” features is

positioned between the “neighboring” features. Accordingly, features described as “vertically neighboring” one another means and includes features of the disclosed identity (or identities) that are located most vertically proximate (e.g., vertically closest to) one another. Moreover, features described as “horizontally neighboring” one another means and includes features of the disclosed identity (or identities) that are located most horizontally proximate (e.g., horizontally closest to) one another.

As used herein, spatially relative terms, such as “beneath,” “below,” “lower,” “bottom,” “above,” “upper,” “top,” “front,” “rear,” “left,” “right,” and the like, may be used for ease of description to describe one element’s or feature’s relationship to another element(s) or feature(s) as illustrated in the figures. Unless otherwise specified, the spatially relative terms are intended to encompass different orientations of the materials in addition to the orientation depicted in the figures. For example, if materials in the figures are inverted, elements described as “below” or “beneath” or “under” or “on bottom of” other elements or features would then be oriented “above” or “on top of” the other elements or features. Thus, the term “below” can encompass both an orientation of above and below, depending on the context in which the term is used, which will be evident to one of ordinary skill in the art. The materials may be otherwise oriented (e.g., rotated 90 degrees, inverted, flipped) and the spatially relative descriptors used herein interpreted accordingly.

As used herein, the singular forms “a,” “an,” and “the” are intended to include the plural forms as well, unless the context clearly indicates otherwise.

As used herein, “and/or” includes any and all combinations of one or more of the associated listed items.

As used herein, the phrase “coupled to” refers to structures operatively connected with each other, such as electrically connected through a direct Ohmic connection or through an indirect connection (e.g., by way of another structure).

As used herein, the term “substantially” in reference to a given parameter, property, or condition means and includes to a degree that one of ordinary skill in the art would understand that the given parameter, property, or condition is met with a degree of variance, such as within acceptable tolerances. By way of example, depending on the particular parameter, property, or condition that is substantially met, the parameter, property, or condition may be at least 90.0 percent met, at least 95.0 percent met, at least 99.0 percent met, at least 99.9 percent met, or even 100.0 percent met.

As used herein, “about” or “approximately” in reference to a numerical value for a particular parameter is inclusive of the numerical value and a degree of variance from the numerical value that one of ordinary skill in the art would understand is within acceptable tolerances for the particular parameter. For example, “about” or “approximately” in reference to a numerical value may include additional numerical values within a range of from 90.0 percent to 110.0 percent of the numerical value, such as within a range of from 95.0 percent to 105.0 percent of the numerical value, within a range of from 97.5 percent to 102.5 percent of the numerical value, within a range of from 99.0 percent to 101.0 percent of the numerical value, within a range of from 99.5 percent to 100.5 percent of the numerical value, or within a range of from 99.9 percent to 100.1 percent of the numerical value.

As used herein, “conductive material” means and includes electrically conductive material such as one or more of a metal (e.g., tungsten (W), titanium (Ti), molybdenum (Mo),

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niobium (Nb), vanadium (V), hafnium (Hf), tantalum (Ta), chromium (Cr), zirconium (Zr), iron (Fe), ruthenium (Ru), osmium (Os), cobalt (Co), rhodium (Rh), iridium (Ir), nickel (Ni), palladium (Pd), platinum (Pt), copper (Cu), silver (Ag), gold (Au), aluminum (Al)), an alloy (e.g., a Co-based alloy, an Fe-based alloy, an Ni-based alloy, an Fe- and Ni-based alloy, a Co- and Ni-based alloy, an Fe- and Co-based alloy, a Co- and Ni- and Fe-based alloy, an Al-based alloy, a Cu-based alloy, a magnesium (Mg)-based alloy, a Ti-based alloy, a steel, a low-carbon steel, a stainless steel), a conductive metal-containing material (e.g., a conductive metal nitride, a conductive metal silicide, a conductive metal carbide, a conductive metal oxide), and a conductively-doped semiconductor material (e.g., conductively-doped polysilicon, conductively-doped germanium (Ge), conductively-doped silicon germanium (SiGe)). In addition, a “conductive structure” means and includes a structure formed of and including conductive material.

As used herein, “insulative material” means and includes electrically insulative material, such one or more of at least one dielectric oxide material (e.g., one or more of a silicon oxide (SiO_x), phosphosilicate glass, borosilicate glass, borophosphosilicate glass, fluorosilicate glass, an aluminum oxide (AlO_x), a hafnium oxide (HfO_x), a niobium oxide (NbO_x), a titanium oxide (TiO_x), a zirconium oxide (ZrO_x), a tantalum oxide (TaO_x), and a magnesium oxide (MgO_x)), at least one dielectric nitride material (e.g., a silicon nitride (SiN_y)), at least one dielectric oxynitride material (e.g., a silicon oxynitride (SiO_xN_y)), at least one dielectric oxycarbide material (e.g., silicon oxycarbide (SiO_xC_y)), at least one hydrogenated dielectric oxycarbide material (e.g., hydrogenated silicon oxycarbide ($\text{SiC}_x\text{O}_y\text{H}_z$)), and at least one dielectric carboxynitride material (e.g., a silicon carboxynitride ($\text{SiO}_x\text{C}_y\text{N}_y$)). Formulae including one or more of “x,” “y,” and “z” herein (e.g., SiO_x , AlO_x , HfO_x , NbO_x , TiO_x , SiN_y , SiO_xN_y , SiO_xC_y , $\text{SiC}_x\text{O}_y\text{H}_z$, $\text{SiO}_x\text{C}_y\text{N}_y$) represent a material that contains an average ratio of “x” atoms of one element, “y” atoms of another element, and “z” atoms of an additional element (if any) for every one atom of another element (e.g., Si, Al, Hf, Nb, Ti). As the formulae are representative of relative atomic ratios and not strict chemical structure, an insulative material may comprise one or more stoichiometric compounds and/or one or more non-stoichiometric compounds, and values of “x,” “y,” and “z” (if any) may be integers or may be non-integers. As used herein, the term “non-stoichiometric compound” means and includes a chemical compound with an elemental composition that cannot be represented by a ratio of well-defined natural numbers and is in violation of the law of definite proportions. In addition, an “insulative structure” means and includes a structure formed of and including insulative material.

As used herein, the term “semiconductor material” refers to a material having an electrical conductivity between those of insulative materials and conductive materials. For example, a semiconductor material may have an electrical conductivity of between about 10^{-8} Siemens per centimeter (S/cm) and about 10^4 S/cm (10^6 S/m) at room temperature. Examples of semiconductor materials include elements found in column IV of the periodic table of elements such as silicon (Si), germanium (Ge), and carbon (C). Other examples of semiconductor materials include compound semiconductor materials such as binary compound semiconductor materials (e.g., gallium arsenide (GaAs)), ternary compound semiconductor materials (e.g., $\text{Al}_x\text{Ga}_{1-x}\text{As}$), and quaternary compound semiconductor materials (e.g., $\text{Ga}_x\text{In}_{1-x}\text{As}_y\text{P}_{1-y}$), without limitation. Compound semicon-

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ductor materials may include combinations of elements from columns III and V of the periodic table of elements (III-V semiconductor materials) or from columns II and VI of the periodic table of elements (II-VI semiconductor materials), without limitation. Further examples of semiconductor materials include oxide semiconductor materials such as zinc tin oxide ($\text{Zn}_x\text{Sn}_y\text{O}$, commonly referred to as “ZTO”), indium zinc oxide ($\text{In}_x\text{Zn}_y\text{O}$, commonly referred to as “IZO”), zinc oxide (Zn_xO), indium gallium zinc oxide ($\text{In}_x\text{Ga}_y\text{Zn}_z\text{O}$, commonly referred to as “IGZO”), indium gallium silicon oxide ($\text{In}_x\text{Ga}_y\text{Si}_z\text{O}$, commonly referred to as “IGSO”), indium tungsten oxide ($\text{In}_x\text{W}_y\text{O}$, commonly referred to as “IWO”), indium oxide (In_xO), tin oxide (Sn_xO), titanium oxide (Ti_xO), zinc oxide nitride (Zn_xON_y), magnesium zinc oxide ($\text{Mg}_x\text{Zn}_y\text{O}$), zirconium indium zinc oxide ($\text{Zr}_x\text{In}_y\text{Zn}_z\text{O}$), hafnium indium zinc oxide ($\text{Hf}_x\text{In}_y\text{Zn}_z\text{O}$), tin indium zinc oxide ($\text{Sn}_x\text{In}_y\text{Zn}_z\text{O}$), aluminum tin indium zinc oxide ($\text{Al}_x\text{Sn}_y\text{In}_z\text{Zn}_w\text{O}$), silicon indium zinc oxide ($\text{Si}_x\text{In}_y\text{Zn}_z\text{O}$), aluminum zinc tin oxide ($\text{Al}_x\text{Zn}_y\text{Sn}_z\text{O}$), gallium zinc tin oxide ($\text{Ga}_x\text{Zn}_y\text{Sn}_z\text{O}$), zirconium zinc tin oxide ($\text{Zr}_x\text{Zn}_y\text{Sn}_z\text{O}$), and other similar materials.

As used herein, the term “homogeneous” means relative amounts of elements included in a feature (e.g., a material, a structure) do not vary throughout different portions (e.g., different horizontal portions, different vertical portions) of the feature. Conversely, as used herein, the term “heterogeneous” means relative amounts of elements included in a feature (e.g., a material, a structure) vary throughout different portions of the feature. If a feature is heterogeneous, amounts of one or more elements included in the feature may vary stepwise (e.g., change abruptly), or may vary continuously (e.g., change progressively, such as linearly, parabolically) throughout different portions of the feature. The feature may, for example, be formed of and include a stack of at least two different materials.

As used herein, the term “integrated circuit” or “integrated-circuit device” may refer to a “microelectronic device” or a “nanoelectronic device,” each of which may be tied to a critical dimension exhibited by inspection. The term “integrated circuit” includes without limitation a memory device, as well as other devices (e.g., semiconductor devices) which may or may not incorporate memory. The term “integrated circuit” may include without limitation a logic device. The term “integrated circuit” may include without limitation a processor device such as a central-processing unit (CPU) or a graphics-processing unit (GPU). The term “integrated circuit” may include without limitation a radiofrequency (RF) device. Further, an “integrated-circuit” device may incorporate memory in addition to other functions such as, for example, a so-called “system on a chip” (SoC) including a processor and memory, or an integrated-circuit device including logic and memory. Further, an “integrated-circuit” device may incorporate memory in addition to other functions such as, for example, a so-called “disaggregated device” where distinct integrated-circuit components are associated to produce the higher function such as that performed by an SoC, including a processor alone, a memory alone, a processor and a memory, or an integrated-circuit device including logic and memory.

As used herein, the term “substrate” means and includes a material (e.g., a base material) or construction upon which additional materials are formed. The substrate may be a semiconductor substrate. The substrate may be a base semiconductor material on a supporting structure, a metal electrode, or a semiconductor substrate having one or more materials, layers, structures, or regions formed thereon. The materials on the semiconductor substrate may include, but

are not limited to, one or more of semiconductor materials, insulating materials, and conductive materials. The substrate may be a conventional silicon substrate or other bulk substrate comprising a layer of semiconductor material. As used herein, the term “bulk substrate” means and includes not only silicon wafers, but also silicon-on-insulator (“SOI”) substrates. The “bulk substrate” may be a SOI substrate such as a silicon-on-sapphire (“SOS”) substrate. The “bulk substrate” may be a SOI substrate such as a silicon-on-glass (“SOG”) substrate. The “bulk substrate” may include epitaxial layers of silicon on a base semiconductor foundation. The “bulk substrate” may include other semiconductor and/or optoelectronic materials. The semiconductor and/or optoelectronic materials may, for example, include one or more of silicon-germanium containing materials, germanium-containing materials, silicon-carbide containing materials, gallium arsenide-containing materials, gallium nitride-containing materials, and indium phosphide-containing materials. The substrate may be doped or undoped.

As used herein, the term “mounting substrate” means and includes structures that are configured to accept an integrated-circuit device. The mounting substrate may be a silicon bridge that is configured to connect more than one integrated-circuit device. The mounting substrate may be a package board that directly contacts an integrated circuit device such as a bare die containing a central-processing unit. The package board may be mounted on a printed wiring board (PWB). The mounting substrate may be a printed wiring board onto which at least one integrated circuit device and/or package board are mounted. The mounting substrate may include a disaggregated device. Unless the context indicates otherwise, the materials described herein may be formed by any suitable technique including, but not limited to, spin coating, blanket coating, chemical vapor deposition (CVD), plasma enhanced CVD (PECVD), atomic layer deposition (ALD), plasma enhanced ALD (PEALD), physical vapor deposition (PVD) (e.g., sputtering), or epitaxial growth. Depending on the specific material to be formed, the technique for depositing or growing the material may be selected by a person of ordinary skill in the art. In addition, unless the context indicates otherwise, removal of materials described herein may be accomplished by any suitable technique including, but not limited to, etching (e.g., dry etching, wet etching, vapor etching), ion milling, abrasive planarization (e.g., chemical-mechanical planarization (CMP)), or other known methods.

FIG. 1 is a simplified top plan of portions of a microelectronic device **101**. The microelectronic device **101** includes an upper memory array device assembly **157** (e.g., FIGS. 2A and 4) that includes array regions **102** (and array subregions, e.g., a first array subregion **102A**), digit line exit regions **104**, word line exit regions **106**, sense amplifier (SA) clusters **240**, sense amplifier exit regions **241**, and paired sub-word line drivers (SWD) **242**, among other structures. The microelectronic device **101** may also include control logic circuitry regions **109**, as well as routing arrangements to different control logic devices (e.g., corresponding to the control logic circuitry **191** (e.g., FIG. 4)) within the different control logic sections, in accordance with embodiments of the disclosure. The array subregions **102**, the digit line exit regions **104**, the word line exit regions **106**, the socket regions **108**, sense amplifier clusters **240**, the sense amplifier exit regions **241**, electrical routing from the array subregions **102** to the sense amplifier clusters **240**, the paired sub-word line drivers **242**, and the control logic circuitry regions **109**, are each described in further detail below. The microelectronic device **101** as illustrated may also include a first base

semiconductor structure **110** that may include semiconductor material **111** and that may be associated with dielectric material **115** (e.g., FIG. 4) such as trench isolation material **113** (e.g., FIG. 4) that may be part of the upper memory array device assembly **157** (e.g., FIGS. 2A and 4).

With continued reference to FIG. 1, the digit line exit regions **104** are also referred to as “digit line contact socket regions” that are interposed between pairs of the array subregions **102** horizontally neighboring one another in a first horizontal direction (e.g., the Y-direction). The digit line exit regions **104** are further defined as odd digit line exit regions **104A** and even digit line exit regions **104B**. The odd digit line exit regions **104A** are further defined as first odd digit line exit regions **104A1** and second odd digit line exit regions **104A2**. The even digit line exit regions **104B** are further defined as first even digit line exit regions **104B1** and second even digit line exit regions **104B2**.

The word line exit regions **106** are also referred to as “word line contact socket regions” that are interposed between additional pairs of the array subregions **102** horizontally neighboring one another in a second horizontal direction (e.g., the X-direction) orthogonal to the first horizontal direction, and one or more socket regions **108** (also referred to as “back end of line (BEOL) contact socket regions”) horizontally neighboring some of the array subregions **102** in one or more of the first horizontal direction and the second horizontal direction. The word line exit regions **106** are further defined as odd word line exit regions **106A** and even word line exit regions **106B**. The odd word line exit regions **106A** are further defined as first odd word line exit regions **106A1** and second odd word line exit regions **106A2**. The even word line exit regions **106B** are further defined as first even word line exit regions **106B1** and second even word line exit regions **106B2**. The array subregions **102** are configured among digit line exit regions **104** and word line exit regions **106**, that may be characterized as digit line exit region odd streets **1040S** and digit line exit region even streets **104ES**, where odd digit line exit regions **104A** are arranged in continuous digit line exit region odd streets **1040S**, and where even digit line exit regions **104B** are arranged in continuous digit line exit region even streets **104ES**. The word line exit regions **106** may be referred to as word line exit region odd avenues **1060A** and word line exit region even avenues **106EA**, where, e.g., odd word line exit regions **106A** are arranged in continuous word line exit region odd avenues **1060A**, and even word line exit regions **106B** are arranged in continuous word line exit region even avenues **106EA**.

The array subregions **102** (also referred to as tiles **102**) of the microelectronic device **101** may comprise horizontal areas of the microelectronic device **101** configured and positioned to have arrays of memory cells (e.g., arrays of DRAM cells) within horizontal boundaries thereof, as described in further detail below. In addition, the array subregions **102** may also be configured and positioned to have desirable arrangements of control logic devices within horizontal boundaries thereof, as also described in further detail below. The control logic devices may include the sense amplifiers **240** and the sub-word line drivers **242**, among other circuitry. The control logic devices are within the horizontal boundaries of the array subregions **102** and may be vertically offset (e.g., in the Z-direction) from the memory cells within the horizontal boundaries of the array regions **102**, and the control logic circuitry may be located in the complementary metal-oxide-semiconductor (CMOS) device assembly **218** (FIG. 4).

The microelectronic device **101** may include a desired quantity of the array subregions **102**. For clarity and ease of understanding of the drawings and related description, FIG. **1** depicts the microelectronic device **101** to include four (4) array subregions **102**: a first array subregion **102A**, a second array subregion **102B**, a third array subregion **102C**, and a fourth array subregion **102D**. The array subregions **102** include respective first and second microelectronic device assemblies (DRAM array devices) **156** and **157** (e.g., FIGS. **2A**, **2B** and **4** also referred to as a lower memory array device assembly **156** and an upper memory array device assembly **157**) as set forth herein. As shown in FIG. **1**, the second array subregion **102B** may horizontally neighbor the first array subregion **102A** in the Y-direction, and may horizontally neighbor the fourth array subregion **102D** in the X-direction; the third array subregion **102C** may horizontally neighbor the first array subregion **102A** in the X-direction, and may horizontally neighbor the fourth array subregion **102D** in the Y-direction; and the fourth array subregion **102D** may horizontally neighbor the third array subregion **102C** in the Y-direction, and may horizontally neighbor the second array subregion **102B** in the X-direction. In additional embodiments, the microelectronic device **101** includes a different number of array subregions **102**. For example, the microelectronic device **101** may include greater than four (4) array subregions **102**, such as greater than or equal to eight (8) array subregions **102**, greater than or equal to sixteen (16) array subregions **102**, greater than or equal to thirty-two (32) array subregions **102**, greater than or equal to sixty-four (64) array subregions **102**, greater than or equal to one hundred twenty eight (128) array subregions **102**, greater than or equal to two hundred fifty six (256) array subregions **102**, greater than or equal to five hundred twelve (512) array subregions **102**, or greater than or equal to one thousand twenty-four (1024) array subregions **102**.

In addition, the microelectronic device **101** may include a desired distribution of the array subregions **102**. As shown in FIG. **1**, in some embodiments, the microelectronic device **101** includes rows **103** of the array subregions **102** extending in the X-direction, and columns **105** of the array subregions **102** extending in the Y-direction. The rows **103** of the array subregions **102** may, for example, include a first row including the first array subregion **102A** and the third array subregion **102C**, and a second row including the second array subregion **102B** and the fourth array subregion **102D**. The columns **105** of the array subregions **102** may, for example, include a first column including the first array subregion **102A** and the second array subregion **102B**, and a second column including the third array subregion **102C** and the fourth array subregion **102D**.

With continued reference to FIG. **1**, the sense amplifiers **240** and the sub-word line drivers **242** are positioned within horizontal boundaries of the array subregions **102**, and in an "open architecture" configuration within the CMOS device assembly **218** that is positioned vertically (Z-direction) above the lower memory array device assembly **156** and the upper memory array device assembly **157**. Open architecture includes, e.g., coupling at least one of selected digit lines **118** (FIGS. **2A** and **2B**) and word lines **120** (FIGS. **2A** and **2B**) from adjacent array subregions **102** where, e.g., signals from digit lines **118** (e.g., FIG. **2A**) and from word lines **120** (e.g., FIG. **2A**) from neighboring array subregions **102** are processed within horizontal boundaries of a single array subregion, e.g., the first array subregion **102A** in the control logic such as within the CMOS device assembly **218** (FIG. **4**). For example between the first array subregion

102A and the second array subregion **102B**, signals from odd digit lines **118A** (e.g., FIG. **2A**) may be received within odd digit line exit regions **104A**, and may be directed to odd sense amplifier **240A** circuit devices. Sense amplifiers **240** are arranged in clusters (e.g., groups) of odd sense amplifiers **240A** and even sense amplifiers **240B**. Sense amplifiers **240** are further arranged in clusters of upper odd sense amplifiers (SA UO) with and lower odd sense amplifiers (SA LO) **240A**. These odd sense amplifiers **240A** refer to sense amplifiers in the CMOS device assembly **218** (FIG. **4**) that process data from upper odd digit lines **118AU** (FIG. **2A**) from the upper memory array device assembly **157** (FIG. **2A**), and from lower odd digit lines **118AL** (FIG. **2B**) from the lower memory array device assembly **156** (FIG. **2B**). Sense amplifiers **240** are further arranged in clusters of upper even sense amplifiers (SA UE) with lower even sense amplifiers (SA LE) **240B**. These lower sense amplifiers **240** refer to sense amplifiers in the CMOS device assembly **218** (FIG. **4**) that process data from digit lines **118** (FIG. **2B**) from the lower memory array device assembly **156** (FIG. **2B**). Further detail is set forth in FIG. **3** of upper and lower sense amplifiers **240** that includes, e.g., arranged clusters of odd sense amplifiers **240A** and arranged clusters of even sense amplifiers **240B**. Further detail of upper and lower sub-word line drivers includes, e.g., arranged pairs of upper odd sub-word line drivers **242A** UO with lower odd sub-word line drivers **242A** LO and arranged pairs of upper even sub-word line drivers **242B** UE with even lower sub-word line drivers **242B** as set forth in FIG. **3**.

With reference to the first array subregion **102A** in FIG. **1**, electrical coupling to the sense amplifier clusters **240**, includes sense amplifier exit regions **241** that may be centrally positioned among a cluster of sense amplifiers **240**. For example a cluster of odd sense amplifiers **240A** includes an odd sense amplifier exit region **241A** that is centrally positioned among the odd sense amplifiers **240A**. Further detail for odd sense amplifiers **240A** and odd sense amplifier exit regions **241A**, include upper odd sense amplifiers (SA UO) and lower odd sense amplifiers (SA LO). The lower odd sense amplifiers (SA LO) are paired centrally and adjacent across the odd sense amplifier exit region **241A**, and the upper odd sense amplifiers (SA UO) are clustered peripherally adjacent the centrally paired lower odd sense amplifiers (SA LO). Further, for example, a cluster of even sense amplifiers **240B** includes an even sense amplifier exit region **241B** that is centrally positioned among even sense amplifiers **240B**. Further detail for even sense amplifiers **240** includes the lower even sense amplifiers (SA LE) are paired centrally and adjacent across the even sense amplifier exit region **241B**, and the upper even sense amplifiers (SA UE) are clustered peripherally adjacent the centrally paired lower even sense amplifiers (SA LE).

With reference to the first array subregion **102A**, electrical coupling to sub-word line drivers **242**, includes lower odd sub-word line drivers (SA LO) that are closer to the word line exit regions **106** than upper odd sub-word line drivers (SA UO) that are paired with a given lower odd sub-word line driver (SA LO). For example a pairing of two odd sub-word line drivers **242A**, includes a lower odd sub-word line driver (SWD LO) that is adjacent an odd word line exit region **106A**, and an upper odd sub-word line driver (SWD UO) is adjacent the lower odd sub-word line driver (SWD LO), such that the lower odd sub-word line driver (SWD LO) is closer to the odd word line exit region **106A**, than is the upper odd sub-word line driver (SWD UO) with which it is paired. Similarly for example, a pairing of two even sub-word line drivers **242B**, includes a lower even sub-word

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line driver (SWD LE) that is adjacent an even sub-word line exit region **106B**, and an upper even sub-word line driver (SWD UE) is adjacent the lower even sub-word line driver (SWD LE), such that the lower even sub-word line driver (SWD LE) is closer to the even word line exit region **106B**, than is the upper even sub-word line driver (SWD UE) with which it is paired. Further detail for coupling digit lines **118** and word lines **120** to respective sense amplifiers and sub-word line drivers is set forth herein.

FIG. 2A is a simplified plan view of the upper memory array device assembly **157** (e.g., FIG. 4), that is part of the microelectronic device **101**. FIG. 2B is a simplified plan view of the lower memory array device assembly **156** (e.g., FIG. 4) that is also part of the microelectronic device **101**. For each of the respective lower and upper memory array device assemblies, **156** and **157**, supporting logic structures (not illustrated), such as decoupling capacitors, may be located within the memory array device assemblies. The lower memory array device assembly **156** may be back-to-front (B2F) physically connected (e.g., physically attached) to the upper memory array device assembly **157** (e.g., FIGS. 4 and 8) by way of at least one bond (e.g., at least one oxide-oxide bond), such as a first oxide-oxide bond of the bottom isolation structure **234** (FIG. 4), as further set forth herein. With continued reference to FIG. 2A, the upper memory array device assembly **157** may be B2F configured between the CMOS device assembly **218** (FIG. 4), and with the lower memory array device assembly **156** (FIGS. 2B and 4), each with at least a bond (e.g., an oxide-oxide bond), such as the first oxide bond of the bottom isolation structure **234** (FIG. 4) that mates the lower memory array device assembly **156** to the upper memory array device assembly **157**, and with at least an additional bond (e.g., an additional oxide-oxide bond), such as an upper, or second oxide bond of the top isolation structure **235** (FIG. 4) that mates the upper memory array device assembly **157** to the CMOS device assembly **218** (FIG. 4). Put another way, the upper memory array device assembly **157** may be attached (e.g., bonded) to the lower memory array device assembly **156** on a first side, and the upper memory array device assembly **157** may be attached (e.g., bonded) to the CMOS device assembly **218** on a second side that is opposite the first side.

With continued reference to FIG. 2A, between the first array subregion **102A** and the second array subregion **102B** of the upper memory array device assembly **157**, upper odd digit line exit regions **104AU** include an individual first upper odd digit line exit region **104A1U** that may be configured and positioned to facilitate electrical connections between a group of upper odd digit lines (e.g., first and third upper odd digit lines **118A1U** and **118A3U**), and an individual second upper odd digit line exit region **104A2U** that may be configured and positioned to facilitate electrical connections between a group of upper odd digit lines (e.g., second and fourth upper odd digit lines **118A2U** and **118A4U**). The several electrical connections facilitate coupling to a group of control logic devices (e.g., upper odd SA devices **240A** (FIGS. 1 and 4)) operatively associated with an upper odd digit lines e.g., **118A1U**. Upper even digit lines are not set forth herein for clarity of the illustrated upper odd digit lines **118AU**, but the upper even digit lines are similarly configured and positioned to be coupled with even digit line exit regions **104B**, and with several electrical connections to facilitate coupling to a group of control logic device (e.g., upper even SA devices **240B** (FIGS. 1 and 4)).

Still referring to FIG. 2A, the word line exit regions **106** of the upper memory array device assembly **157** of the

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microelectronic device **101** may comprise horizontal areas that are configured and positioned to have at least some word lines **120** (e.g., access lines) horizontally terminate therein. The word lines **120** extend below the array subregions **102** in the second direction (X-direction, FIG. 4). For an individual word line exit region **106**, at least some word lines **120** operatively associated with the array subregions **102** flanking (e.g., at opposing boundaries in the X-direction) the word line exit region **106** may have ends within the horizontal boundaries of the word line exit region **106**. In addition, the word line exit regions **106** may also be configured and positioned to include contact structures and routing structures within the horizontal boundaries thereof that are operatively associated with the word lines **120**. As described in further detail below, some of the contact structures within the word line exit regions **106** may couple the word lines **120** to control logic circuitry of additional control logic devices (e.g., sub-word line driver (SWD) devices) that are positioned in the CMOS device assembly **218** (e.g., FIG. 4). For example a first upper odd word line **120A1U** and a third upper odd word line **120A3U** are coupled to a first odd word line exit region **106A1** that is horizontally between the first array subregion **102A** and the third array subregion **102C**. Even word lines **120B** are similarly illustrated but further detail is not set forth for the sake of brevity and simplicity, except the even word lines **120B** are coupled to even word line exit regions **106B**.

With continued reference to FIG. 2A, the socket regions **108** of the upper memory array device assembly **157** of the microelectronic device **101** may comprise horizontal areas of the microelectronic device **101** configured and positioned to facilitate electrical connections (e.g., by way of contact structures and routing structures formed within horizontal boundaries thereof) between control logic circuitry region **109** and additional structures (e.g., back-end-of-line (BEOL) structures), as described in further detail below. The socket regions **108** may horizontally neighbor one or more peripheral horizontal boundaries (e.g., in the Y-direction, in the X-direction) of one or more groups of the array subregions **102**. For clarity and ease of understanding of the drawings and related description, FIG. 2A depicts the upper memory array device assembly **157** of the microelectronic device **101** to include one (1) socket region **108** horizontally neighboring a shared horizontal boundary of a control logic circuitry region **109**, which is horizontally neighboring a shared horizontal boundary of the second array subregion **102B** and the fourth array subregion **102D**. However, the upper memory array device assembly **157** of the microelectronic device **101** may be formed to include one or more of a different quantity and a different horizontal position of socket region(s) **108** and control logic circuitry region(s) **109**. As a non-limiting example, the socket region **108** may horizontally neighbor a shared horizontal boundary of a different group of the array subregions **102** (e.g., a shared horizontal boundary of the third array subregion **102C** and the fourth array subregion **102D**, a shared horizontal boundary of the first array subregion **102A** and the third array subregion **102C**, a shared horizontal boundary of the first array subregion **102A** and the second array subregion **102B**). As another non-limiting example, the microelectronic device **101** may be formed to include multiple (e.g., a plurality of, more than one) socket regions **108** horizontally neighboring different groups of the array subregions **102** than one another. In some embodiments, multiple socket regions **108** collectively substantially horizontally surround (e.g., substantially horizontally circumscribe) the array subregions **102**.

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FIG. 2B is a simplified plan view of the lower memory array device assembly 156. The lower memory array device assembly 156 may be configured with the upper memory array device assembly 157, stacked (folded, oxide-oxide bonded, coupled) above it (FIG. 4). With continued reference to FIG. 2B, the lower memory array device assembly 156 may be positioned below the upper memory array device assembly 157 (FIGS. 2A and 4), and the upper memory array device assembly 157 may be positioned below the CMOS device assembly 218 (FIG. 4).

Similar to the upper memory array device assembly 157 (FIG. 2A), the lower memory array device assembly 156 has analogous structures. As described in further detail herein, between a first array subregion 102A and a second array subregion 102B, odd digit line exit regions 104A include an individual first lower odd digit line exit region 104AL1 that may be configured and positioned to facilitate electrical connections between a group of lower odd digit lines (e.g., first and third lower odd digit lines 118A1L and 118A3L), and an individual second lower digit line exit region 104AL2 may be configured and positioned to facilitate electrical connections between a group of lower odd digit lines (e.g., second and fourth lower odd digit lines 118A2L and 118A4L, FIG. 2A), and a group of control logic devices (e.g., lower odd SA devices, FIGS. 1 and 4) operatively associated with lower odd digit lines. Still referring to FIG. 2B, the lower word line exit regions 106L of the lower memory array device assembly 156 of the microelectronic device 101 may comprise horizontal areas of the lower memory array device assembly 156 of the microelectronic device 101 configured and positioned to have at least some word lines 120 (e.g., access lines) horizontally terminate therein. The word lines 120 extend below the array subregions 102 in a second direction (X-direction, FIG. 4). For an individual word line exit region 106, at least some word lines 120 operatively associated with the array subregions 102 flanking (e.g., at opposing boundaries in the X-direction) the word line exit region 106 may have ends within the horizontal boundaries of the word line exit region 106. In addition, the word line exit regions 106 may also be configured and positioned to include contact structures and routing structures within the horizontal boundaries thereof that are operatively associated with the word lines 120. As described in further detail below, some of the contact structures within the word line exit regions 106 may couple the word lines 120 to control logic circuitry of additional control logic devices (e.g., sub-word line driver (SWD) devices) that are positioned in the CMOS device assembly 218 (e.g., FIG. 4). For example a first lower odd word line 120A1L and a third lower odd word line 120A3L are coupled to a lower first odd word line exit region 106A1 that is horizontally between the first array subregion 102A and the third array subregion 102C. Even word lines 120B are also set forth in simplified detail, and the even word lines 120B are coupled to even word line exit regions 106B.

With continued reference to FIG. 2B, the socket regions 108 of the lower memory array device assembly 156 of the microelectronic device 101 may horizontally correspond (X-direction and Y-direction) to socket regions 108 of the upper memory array device assembly 157 (FIG. 2A) to facilitate electrical connections (e.g., by way of contact structures and routing structures formed within horizontal boundaries thereof) between control logic circuitry region 109 and additional structures (e.g., back-end-of-line (BEOL) structures), as described in further detail below.

FIG. 3 is a simplified plan view of selected structures of the microelectronic device 101 depicted in FIGS. 1, 2A, 2B,

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and 4, with illustrative examples of selected first and third lower odd digit lines 118A1L and 118A3L, and selected upper odd digit lines 118A1U and 118A3U. The several selected first and third lower odd digit lines 118A1L and 118A3L and the several selected upper odd digit lines 118A1U and 118A3U may be coupled with at least some conductive features within a first odd digit line exit region 104A1. In addition, the at least some conductive features within the first odd digit line exit region 104A1 may be coupled to the cluster of odd sense amplifiers 240 located in the CMOS device assembly 218 (FIG. 4) within horizontal boundaries of the first array subregion 102A. Similarly, illustrative examples of selected first and third lower odd word lines 120A1L and 120A3L, and selected first and third upper odd word lines 120A1U and 120A3U may be coupled at least some additional conductive features within a first odd word line exit region 106A1. Even digit lines 118B and even word lines 120B are not set forth in FIG. 3 for clarity as ease of understanding the drawings and associated description, but such even digit and word lines may be coupled to at least some further conductive features with respective even digit line exit regions 104B and even word line exit regions 106B.

Further referring to FIG. 3, the microelectronic device 101 includes the selected first and third lower odd digit lines 118A1L and 118A3L from the lower memory array device assembly 156 (FIG. 2B), and the selected upper odd digit lines 118A1U and 118A3U from the upper memory array device assembly 157 (FIG. 2A). The open architecture includes coupling at least two of selected digit lines 118 from adjacent array subregions 102 where, e.g., signals from digit lines 118 from neighboring array subregions 102 may be processed within horizontal boundaries of a single array subregion 102 in the control logic device assembly such as within the CMOS device assembly 218 (FIG. 4). For example between the first array subregion 102A and the second array subregion 102B, signals from first and third lower odd digit lines 118A1L and 118A3L may be received within a first odd digit line exit region 104A1, and may be directed to lower odd sense amplifier circuit devices 240A LO1 and 240A LO2, respectively. Further for example between the first array subregion 102A and the second array subregion 102B, signals from first and third upper odd digit lines 118A1U and 118A3U may be received within the first odd digit line exit region 104A1, and may be directed to upper odd sense amplifier circuit devices 240A UO1 and 240A UO2, respectively.

With reference to the first array subregion 102A, sense amplifier exit regions 241 may individually be centrally positioned among a cluster of sense amplifiers 240 and may individually include conductive features (e.g., conductive routing) in electrical communication with the cluster of sense amplifiers 240. For example, a cluster of odd sense amplifiers 240A may have an odd sense amplifier exit region 241A centrally positioned among the odd sense amplifiers 240A. Further detail for odd sense amplifiers 240A and odd sense amplifier exit regions 241A, include upper odd sense amplifiers 204A UO1 and 240A UO2, and lower odd sense amplifiers 204A LO1 and 240A LO2. The lower odd sense amplifiers 240A LO1 and 240A LO2 may be paired centrally adjacent and across the odd sense amplifier exit region 241A, and the upper odd sense amplifiers 240A UO1 and 240A UO2 may be horizontally positioned peripherally adjacent the paired lower odd sense amplifiers 240A LO1 and 240A LO2. Further, for example, a cluster of even sense amplifiers 240B may have an even sense amplifier exit region 241B centrally positioned among even sense ampli-

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fiers **240B**. Further detail for even sense amplifiers **240B** includes the lower even sense amplifiers **240B LE1** and **240B LE2** that may be paired centrally adjacent and across the even sense amplifier exit region **241B**, and the upper even sense amplifiers **240B UE1** and **240B UE2** that may be horizontally positioned peripherally adjacent the paired even lower sense amplifiers **240B LE1** and **240B LE2**.

With reference to the first array subregion **102A**, lower odd sub-word line drivers **242A LO** may individually include conductive features (e.g., conductive routing) in electrical communication with the sub-word line drivers **242**, and may individually be closer to the odd word line exit regions **106A** (e.g., the first odd word line exit region **106A1**) than to upper odd sub-word line drivers **242A UO** that are paired with a given lower odd sub-word line driver **242A LO**. Similarly for example, a pairing of two even sub-word line drivers **242B**, may include a lower even sub-word line driver **242B LE** adjacent a first even word line exit region **106B1**, and an upper even sub-word line driver **242B UE** adjacent the lower even sub-word line driver **242B LE**. The lower even sub-word line driver **242B LE** may be closer to the even word line exit region **106B** than is the upper even sub-word line driver **242B UE** with which it is paired.

FIG. 4 is a simplified, transverse, cross-section elevation view of selected structures of the microelectronic device **101** that include the lower memory array device assembly **156**, the upper memory array device assembly **157**, and the CMOS device assembly **218**, according to several embodiments. The cross-section view is taken at an angle γ' to the first direction (Y-directions) such as about 21 to illustrate both digit lines **118** and word lines **120** in cross section. Further, the word lines **120** are formed within a word line gate oxide material **123**. The lower memory array device assembly **156** may be referred to as a first microelectronic device assembly **156**, the upper memory array device assembly **157** may be referred to as a second microelectronic device assembly **157**, and the CMOS device assembly **218** may be referred to as a third microelectronic device assembly **218**. The cross-section view may be taken from the section A in FIG. 3, where the cross-section view includes the first array subregion **102A** for both the first microelectronic device assembly **156** and the second microelectronic device assembly **157**, the second array subregion **102B** also for both the first microelectronic device assembly **156** and the second microelectronic device assembly **157**, portions of the third microelectronic device assembly **218** that are superimposed above the second microelectronic device assembly **157**, and the section A is particularly expanded to include the first digit line exit region **104A1** with the first and third lower odd digit lines **118A1L** and **118A3L**, and the first and third upper odd digit lines **118A1U** and **118A3U**.

Referring to FIG. 4, the third microelectronic device assembly **218** (e.g., CMOS device structure, CMOS device wafer) includes control logic circuitry **191**, SWD sections **242** of the control logic circuitry **191**, SA sections **240** of the control logic circuitry **191**, and additional control logic circuitry **191** such as read-write gap (RW_gap) circuitry (not illustrated) and other circuitry.

Lateral (Y-direction) boundaries may be defined at the level of the first microelectronic device assembly **156** and the second microelectronic device assembly **157**. Overall for the microelectronic device **101** as depicted in FIG. 4, the odd digit line exit region boundaries may be defined by an odd digit line socket region **218AD**, that is within the third microelectronic device assembly **218** and located between the first array subregion **102A** and the second array sub-

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region **102B**. Similarly overall for the microelectronic device **101**, the even digit line exit region boundaries may be defined by an even digit line socket region **218BD**, that is within the third microelectronic device assembly **218**, and adjacent left to the first array subregion **102A**.

Lateral first-direction (Y-direction) boundaries are defined at the level of the first microelectronic device assembly **156**. The lateral first-direction boundaries include a first lower odd digit line socket region **156A D1** for the first lower odd digit line exit region **104A1L** (e.g., seen in FIG. 3 as **104A1**, between the first array subregion **102A** and the second array subregion **102B**) by base semiconductor material **110** and dielectric material **114** that fills the first lower odd digit line socket region **156A D1** for the first lower odd digit line exit region **104A1L**, where the dielectric material **114** is also present among other regions. The dielectric material **114** is depicted generally, and particularly as a filled trench **112** among transistor structures, but the dielectric material **114** may be present in several separate structures among the base semiconductor material **110** of the first (lower) microelectronic device assembly **156**, where the several separate structures of the dielectric material **114** are achieved by techniques that depend upon processing choices. Similarly, lateral (Y-direction) boundaries are defined at the level of the first microelectronic device assembly **156**, at a first lower even digit line socket region **156B D1** for the first lower even digit line exit region **104B1L** (e.g., seen in FIG. 3 as **104B1** adjacent left the first array subregion **102A**). The first lower even digit line socket region **156B D1** is laterally across from the first lower odd digit line socket region **156A D1**, where the dielectric material **114** fills boundaries defined by the base semiconductor material **110**.

Lateral first-direction boundaries are also defined at the level of the second microelectronic device assembly **157**. The lateral first-direction boundaries include a first upper odd digit line socket region **157A D1** for the first upper odd digit line exit region **104A1U** (e.g., seen in FIG. 3 as **104A1**) by base semiconductor material **111** and dielectric material **115** that fills the first upper odd digit line socket region **157A D1**, where the dielectric material **115** is also present among other regions. The dielectric material **115** is depicted generally, and particularly as a filled trench **113**, but the dielectric material **115** may be present in several separate structures among the base semiconductor material **111**, where the several separate structures of the dielectric material **115** are achieved by techniques that depend upon processing choices. Similarly, boundaries are defined for the second microelectronic device assembly **157** at a first upper even digit line socket region **157B D1** for the first even digit line exit region **104B1** (seen in FIG. 3 as **104B1** adjacent the first array subregion **102A**). The first upper even digit line socket region **157B D1** is laterally across from the first upper odd digit line socket region **157A D1**, where the dielectric material **115** fills boundaries defined by the base semiconductor material **111**. The first upper odd digit line socket region **157A D1** is wider than the first lower odd digit line socket region **156A D1**, such that a "window" exists at the first-direction (Y-direction) lateral boundaries of the base semiconductor material **111**, through dielectric material **115**, and encompasses the first lower odd digit line socket region **156A D1** in a rectangular framing configuration when observed from a top plan view. The rectangular framing configuration of the first upper odd digit line socket region **157A D1** may only be larger than the first lower odd digit line socket region **156A D1** in the first direction (Y-direction). Similarly it is observed that the first upper even digit line socket region **157B D1** is wider than the first lower even

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digit line socket region **156B D1**, such that a window is created at the boundaries of the base semiconductor material **111**, through dielectric material **115**, and encompasses the first lower even digit line socket region **156B D1** in a rectangular framing configuration when observed from a top plan view. The rectangular framing configuration of the first upper even digit line socket region **157B D1** may only be larger than the first lower even digit line socket region **156B D1** in the first direction (Y-direction).

Further referring to FIG. 4 for clarity, the first microelectronic device assembly **156** is set forth in some detail at the second array subregion **102B**, and the first microelectronic device assembly **156** is set forth more generally at the first array subregion **102A**. Similarly but contrariwise referring to FIG. 4, the second microelectronic device assembly **157** is set forth in some detail at the first array subregion **102A**, and the second microelectronic device assembly **157** is set forth more generally at the second array subregion **102B**. Similar structures among the first microelectronic device assembly **156** and the second microelectronic device assembly **157** may be enumerated with identical reference numerals. The base semiconductor material **110** of the first microelectronic device assembly **156**, however, is distinguished from the base semiconductor material **111** of the second microelectronic device assembly **157**. Similarly, the dielectric material **114** of the first microelectronic device assembly **156** is distinguished from the dielectric material **115** of the second microelectronic device assembly **157**.

Further referring to FIG. 4, both the first microelectronic device assembly **156** and the second microelectronic device assembly **157** include array subregions **102** of the microelectronic device **101** that are configured and positioned to have arrays of memory cells (e.g., arrays of DRAM cells) positioned within horizontal boundaries (e.g., horizontal areas) thereof, as described in further detail below. In addition, the array subregions **102** (e.g., the first array subregion **102A**, the second array subregion **102B**, the third array subregion **102C** (e.g., FIG. 3), and the fourth array subregion **102D** (e.g., FIG. 3)) may also be configured and positioned to have desirable arrangements of the control logic circuitry **191** that are positioned within horizontal boundaries thereof, as also described in further detail below. The control logic circuitry **191** may be vertically offset (e.g., vertically overlie, in the Z-direction) from the memory cells in the second microelectronic device assembly **157**.

The following refers to the first microelectronic device assembly **156**, and it may also refer to the second microelectronic device assembly **157**. Referring collectively to FIGS. 2A, 2B, 3, and 4, the first microelectronic device assembly **156** includes arrays of memory cells **146** positioned within horizontal areas of the array subregions **102**. At least some of the different control logic circuitry **191** of the third microelectronic device assembly **218** may be coupled to the memory cells **146** of the first microelectronic device assembly **156**. Similarly for the second microelectronic device assembly **157**, memory cells **146** are positioned within horizontal areas of the array subregions **102**. For clarity and ease of understanding the description, not all features (e.g., structures, materials, regions, devices) of the microelectronic device **101** described below with reference to FIGS. 1, 2A, 2B, and 3 are illustrated in FIG. 4.

In an embodiment for the first microelectronic device assembly **156**, the first base semiconductor structure **110** includes the only semiconductor material in the first microelectronic device assembly **156**. Accordingly, an open architecture may facilitate different arrangements of odd digit lines **118A** (FIG. 2B) enumerated, e.g., 1, 3, 5, 7 . . . (n+1),

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and even digit lines **118B** (FIG. 2A), enumerated e.g., 0, 2, 4, 6 . . . n. The odd digit lines **118A** (FIG. 2B) may emerge from two horizontally neighboring array subregions **102** (FIG. 2B), at an odd digit line exit region **104A** (FIG. 2B). The even digit line exit regions **104B** (FIG. 2B) may emerge from two other horizontally neighboring array subregions **102** (FIG. 2B), at an even digit line exit region **104B** (FIG. 2B). As illustrated in FIG. 4, access devices **116** (e.g., access transistors) may be located within boundaries of the array subregion **102** (FIGS. 2A and 2B). In addition, digit lines **118** (FIGS. 2A and 2B, e.g., data lines, bit lines) may be located to be coupled to the access devices **116** (FIG. 2A) and to horizontally extend in the Y-direction through the array subregion **102** (FIG. 2A). At least some of the digit lines **118** (FIGS. 2A and 2B) may terminate (e.g., end) within the digit line exit regions **104** (FIG. 2B). Furthermore, word lines **120** (e.g., access lines, FIG. 8) may be configured to be coupled to the access devices **116** (FIGS. 2A and 2B) and to horizontally extend in the X-direction through the array subregion **102** (FIG. 2A). At least some of the word lines **120** (FIGS. 2A through 2C) may terminate within the word line exit regions **106** (FIG. 2C).

The access devices **116** located within the array subregion **102** may be employed as components of memory cells (e.g., DRAM cells) located within the array subregion **102**. By way of non-limiting example, each access device **116** may individually include a channel region comprising a portion of the first base semiconductor structure **110**; a source region and a drain region each individually comprising one or more of at least one conductively doped portion of the first base semiconductor structure **110** and/or at least one conductive structure formed in, on, or over the first base semiconductor structure **110**; and at least one gate structure comprising a portion of at least one of the digit lines **118**. Each access device **116** may also include a gate dielectric material (e.g., a dielectric oxide material) formed to be interposed between the channel region thereof and the gate structure thereof.

The digit lines **118** may exhibit horizontally elongate shapes extending in parallel in the Y-direction; and the word lines **120** may exhibit horizontally elongate shapes extending in parallel in the X-direction orthogonal to the Y-direction. As used herein, the term "parallel" means substantially parallel. The digit lines **118** and the word lines **120** may each individually include conductive material. By way of non-limiting example, the digit lines **118** and the word lines **120** may each individually include one or more of at least one metal, at least one alloy, and at least one conductive metal-containing material (e.g., a conductive metal nitride, a conductive metal silicide, a conductive metal carbide, a conductive metal oxide). In some embodiments, the digit lines **118** and the word lines **120** each individually include one or more of W, Ru, Mo, and titanium nitride (TiN_y).

For the first microelectronic device assembly **156**, the first lower odd digit line **118A1L** exits the first array subregion **102A** into the first lower odd digit line exit region **104A1L** within the first lower odd digit line socket region **156A D1**, and the third lower odd digit line **118A3L** exits the second array subregion **102B** into the first lower odd digit line exit region **104A1L** within the first lower odd digit line socket region **156A D1**. For the second microelectronic device assembly **157**, the first upper odd digit line **118A1U** exits the first array subregion **102A** into the first odd digit line exit region **104A1** within the first upper odd digit line socket region **157A D1**, and the third upper odd digit line **118A3U** exits the second array subregion **102B**, also into the first upper odd digit line exit region **104A1U** within the first upper odd digit line socket region **157A D1**. Consequently

for both first and second microelectronic device assemblies **156** and **157**, odd digit lines **118A** from adjacent array subregions **102A**, **102B** may be received in a common odd digit line exit region **104A1**, and electrical connections for the odd digit lines **118A** so enumerated, couple the third microelectronic device assembly **218** with the respective first and second microelectronic device assemblies **156** and **157**.

Within the array region **102** for each of the respective first and second microelectronic device assemblies **156** and **157**, additional features (e.g., structures, materials) are also located on, over, and/or between the access devices **116**, the digit lines **118**, and the word lines **120**. For example, as shown in FIG. 4, first contact structures **122** (e.g., digit line contact structures, also referred to as so-called “bitcon” structures) may be configured to vertically extend between and couple the access devices **116** to the digit lines **118**; second contact structures **124** (e.g., cell contact structures, also referred to as so-called “cellcon” structures) may be in contact with the access devices **116** and may be coupled to the access devices **116** to storage node devices (e.g., capacitors); dielectric cap structures **126** may be on or over the digit lines **118**; and additional dielectric cap structures **128** may be on or over the word lines **120**. In addition, dielectric structures (e.g., dielectric spacers, such as low-k dielectric spacers formed of and including one or more low-k dielectric materials) may intervene (e.g., horizontally intervene) between and isolate the second contact structures **124** and digit lines **118**; and further dielectric structures (e.g., gate dielectric structures, such as gate dielectric oxide structures) may intervene (e.g., horizontally intervene) between and isolate the first contact structures **122** and the word lines **120**.

The first contact structures **122** and the second contact structures **124** may individually include at least one conductive material. In some embodiments, the first contact structures **122** and the second contact structures **124** individually include one or more of at least one metal (e.g., W), at least one alloy, at least one conductive metal silicide (e.g., one or more of titanium silicide (TiSi_x), cobalt silicide (CoSi_x), tungsten silicide (WSi_x), tantalum silicide (TaSi_x), molybdenum silicide (MoSi_x), and nickel silicide (NiSi_x)), and at least one conductive metal nitride (e.g., one or more of TiN_y , tungsten nitride (WN_y), tantalum nitride (TaN_y), cobalt nitride (CoN_y), molybdenum nitride (MoN_y), and nickel nitride (NiN_y)). In addition, the dielectric cap structures **126** and the additional dielectric cap structures **128** may individually include at least one insulative material. In some embodiments, the dielectric cap structures **126** and the additional dielectric cap structures **128** are individually formed of and include a dielectric nitride material (e.g., SiN_y , such as Si_3N_4).

As shown in FIG. 4, for each of the first microelectronic device assembly **156** and the second microelectronic device assembly **157**, within the array regions **102**, at least one first routing tier **134** including first routing structures **136** may be located over the access devices **116**; and storage node devices **138** (e.g., capacitors) may be located over and in electrical communication with at least some of the first routing structures **136**; and a second routing tier **142** including second routing structures **144** may be located over the storage node devices **138**.

The first routing structures **136** of the first routing tier **134** may be employed to facilitate electrical communication between additional features (e.g., structures, materials, devices) coupled thereto. In some embodiments, at least some of the first routing structures **136** couple the access

devices **116** to the storage node devices **138** to form the memory cells **146**. The first routing structures **136** may serve as redistribution structures to operatively connect an array of the access devices **116** having a first layout configuration to an array of the storage node devices **138** having a second, different layout configuration. The first routing structures **136** may each individually include conductive material. By way of non-limiting example, the first routing structures **136** may include one or more of at least one metal, at least one alloy, and at least one conductive metal-containing material (e.g., a conductive metal nitride, a conductive metal silicide, a conductive metal carbide, a conductive metal oxide). In some embodiments, the first routing structures **136** are formed of and include W.

Still referring to FIG. 4, within the first microelectronic device assembly **156**, interconnection of the digit lines **118** to the sense amplifiers **240** in the third microelectronic device assembly **218** includes first and third lower digit line interconnects **298D1L** and **298D3L**. The first and third lower digit line interconnects **298D1L** and **298D3L** may also be referred to as lower “vertical digit line contacts” (LVDL-CON) **298DL**. The first and third lower vertical digit line contacts **298D1L** and **298D3L** may contact (e.g., physically contact, electrically contact) portions of the second routing structures **144** of the second routing tier **142** within the first microelectronic device assembly **156**, within horizontal areas of the digit line exit regions **104**. In an embodiment, the first and third lower digit line interconnects **298D1L** and **298D3L** are individually substantially monolithic (e.g., unitary) and vertically extend (e.g., in the Z-direction) at least between the respective first and third lower odd digit lines **118A1L** and **118A3L**, and the second routing tier **142** within the first microelectronic device assembly **156**. In an embodiment, one or more of the first and third lower digit line interconnects **298D1L** and **298D3L** vertically extend into the respective first and third lower odd digit lines **118A1L** and **118A3L**. In an embodiment, a vertical height of each of the respective first and third lower digit line interconnects **298D1L** and **298D3L** is greater than a combined vertical height of the first routing structures **136** and the storage node devices **138** within the first microelectronic device assembly **156**.

Further interconnection of portions of the respective first and third lower odd digit lines **118A1L** and **118A3L** within the digit line exit regions **104** to the sense amplifiers **240** includes second conductive routing structure assemblies **299** that may include second redistribution structure pads **299** at a K1 redistribution layer within the first microelectronic device assembly **156** at a bottom isolation structure **234** that may be at the same level as the second routing tier **142** of the first microelectronic device assembly **156**. The second redistribution structure pads **299** may be part of conductive routing structure assemblies at a K1 level within the first microelectronic device assembly **156**. The bottom isolation structure **234** includes isolation materials **164** of the first microelectronic device assembly **156** and isolation materials **226** of the second microelectronic device assembly **157**. Further interconnection of portions of the respective first and third lower odd digit lines **118A1L** and **118A3L** within the digit line exit regions **104** to the sense amplifiers **240** includes third conductive routing structure assemblies **301** that may include third interface contact pads at the K2 redistribution layer within the second microelectronic device assembly **157** that may couple to, e.g., odd sense amplifiers **240A** with lateral interconnects **199** (e.g., FIG. 5) within the third conductive routing structure assembly **301** at the K2 redistribution layer. The conductive contact pads of

the third conductive routing structure assemblies **301** may directly contact subsequent lower digit line contacts **298D1LS** coupled to the first lower digit line interconnects **298D1L**. The subsequent lower interconnect **218D1LS** may be located at the same elevation (Z-height) as the first and third upper digit line contacts **298D1U** and **298D3U**. Other electrical structures may intervene between the first lower digit line interconnects **298D1L** and the subsequent lower digit line contacts **298D1LS**. The lateral interconnects **199** (e.g., FIG. 5, horizontal conductive routing structures) may extend transversely from and out of the digit line exit regions **104** within the conductive routing structure assembly of the K2 redistribution layer, and the lateral interconnect **199** (e.g., FIG. 5) to the sense amplifiers **240**, where the sense amplifiers **240** are vertically above (Z-direction) memory cells **146** (FIGS. 2A and 2B) within the array subregions **102** of the respective first and second microelectronic device assemblies **156** and **157**. Similarly, interconnection of portions of the respective first and third upper odd digit lines **118A1U** and **118A3U** within the digit line exit regions **104** to the sense amplifiers **204** may include the interface contact pads of the third conductive routing structure assembly **301** at the K2 redistribution layer within the second microelectronic device assembly **157** at the top isolation structure **235**.

FIG. 5 is a simplified top plan view of portions of a cluster of odd sense amplifiers **240A** of the third microelectronic device assembly **218** (FIG. 4) within the first array subregion **102A**, according to several embodiments. In general control, the control logic circuitry **191** depicted in, e.g., FIG. 4, is specifically set forth as a portion of control logic circuitry **291** in FIG. 5. The first odd sense amplifier exit region **241A1** may be located centrally among a bilateral cluster of odd sense amplifiers **240**. The first odd sense amplifier exit region **241A1** is schematically connected to the first odd digit line exit region **104A1**, indicated by dashed lines. The conductive routing structure assembly that includes the interface contact pads of the third conductive routing structure assembly **301** (FIG. 4) are depicted schematically at boundaries of the first odd digit line exit region **104A1** at the K2 redistribution level (FIG. 4). Other interface contact pads of the third conductive routing structure assembly **301** are also schematically depicted at boundaries of the first odd sense amplifier exit region **241A1** at the K2 redistribution level (FIG. 4). The lower first odd sense amplifier **240A LO1** (also FIG. 3) and the lower second odd sense amplifier **240A LO2** (also FIG. 3) are paired horizontally across from and adjacent the first odd sense amplifier exit region **241A1**. The upper first odd sense amplifier **240A UO1** (also FIG. 3) and the upper second odd sense amplifier **240A UO2** (also FIG. 3) are clustered peripherally adjacent the respective lower first odd sense amplifier **240A LO1** and the lower second odd sense amplifier **240A LO2**.

Individual sub-circuitry within a given sense amplifier section is represented in simplified form, both with functional acronyms and relative position. For example in the lower first odd sense amplifier **240A LO1** column select (CS) circuitry is adjacent the boundaries of the first odd sense amplifier exit region **241A1**. Adjacent the CS circuitry in the lower first odd sense amplifier **240A LO1**, is NMOS sense amplifier sub-circuitry (NSA), and adjacent the NSA is voltage transfer characteristic (VTC) sense amplifier sub-circuitry. Further and adjacent the VTC sense amplifier sub-circuitry is PMOS sense amplifier sub-circuitry (PSA). The balance of the first odd sense amplifier **240A LO1** is a "mirror image" repetition of sub-circuitry: PSA, VTC, and NSA to complete simplified sub-circuitry within the first odd sense amplifier **240A LO1**.

Lower lateral interconnects **199L** of the conductive routing structure assemblies each exit the first odd sense amplifier exit region **241A1**, and each lower lateral interconnect **199L** couples to CS sub-circuitry within the respective lower first and second odd sense amplifier assemblies **240A LO1** and **240A LO2**. Upper lateral interconnects **199U** each exit the first odd sense amplifier exit region **241A1**, and each upper lateral interconnect **199U** couples to CS circuitry within the respective upper first and second odd sense amplifiers **240A UO1** and **240A UO2**. In an embodiment, a given lower lateral interconnect **199L** has a shorter routing path (shorter length, shorter physical distance) from a sense amplifier exit region **241** to the corresponding lower sense amplifier **240L**, than the corresponding upper lateral interconnect **199U** to the corresponding upper sense amplifier **240U**. Put another way, a given lower sense amplifier **240L** may be coupled with a lower lateral interconnect **199L** within the conductive routing structure assemblies at the K2 routing level from third contact pads of the third conductive routing structure assembly **301** at the sense amplifier exit region **241**, with a shorter routing distance, than the corresponding upper sense amplifier **240U** may be coupled with an upper lateral interconnect **199U**, also and the K2 routing level from the contact pads of the third conductive routing structure assembly **301** at the sense amplifier exit region **241**. In an embodiment, the CS circuitry for the lower sense amplifier **240L** is located closer to the sense amplifier exit region **241**, than is the CS circuitry for the upper sense amplifier **240U**. In FIG. 5, the CS circuitries for adjacent lower and upper sense amplifier assemblies **240** are at opposite boundaries of each half of the sense amplifier cluster **240**. Even sense amplifiers **240B** may also be similarly arranged such that routing from the even sense amplifier exit regions **241B** is shorter to CS circuitry for lower even sense amplifiers **240B** than to upper even sense amplifiers **240B**. In an embodiment read-write gap (RW_gap) circuitry is located elsewhere within the CMOS device assembly **218** (e.g., FIGS. 3 and 4), such that it is distant from the sense amplifier cluster **240**, but the RW_gap circuitry may be located between a sense amplifier cluster **240** and a paired sub-word line driver circuitry **242** (e.g., FIG. 3).

FIG. 6 is a simplified top plan view of portions of a cluster of odd sense amplifiers **240A** depicted in the third microelectronic device assembly **218** (FIG. 4) within the first array subregion **102A**, according to several embodiments. In general, a portion of the control logic circuitry **191** depicted in, e.g., FIG. 4, is specifically set forth as a portion of control logic circuitry **391** in FIG. 6. The first odd sense amplifier exit region **241A1** may be located centrally among the cluster of odd sense amplifiers **240A**. For clarity and simplicity, in FIG. 6, while it will be understood that features of the first odd sense amplifier exit region **241A1** and the first odd digit line exit region **104A1** are coupled to one another, no schematic coupling is depicted, in order to clearly illustrate lower and upper lateral interconnects **199L** and **199U**. The interface contact pads of the third conductive routing structure assembly **301** (FIG. 4) are depicted schematically at boundaries of the first odd digit line exit region **104A1** at conductive routing structure assemblies that include the K2 redistribution level (FIG. 4). Other interface contact pads of the third conductive routing structure assembly **301** are also schematically depicted at boundaries of the first odd sense amplifier exit region **241A1** at conductive routing structure assemblies that include the K2 redistribution level (FIG. 4). The lower first odd sense amplifier **240A LO1** and the lower second odd sense amplifier **240A LO2** are bilaterally paired

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horizontally across from and adjacent the first odd sense amplifier exit region **241A1**. The upper first odd sense amplifier **240A UO1** and the upper second odd sense amplifier **240A UO2** are clustered peripherally adjacent the respective lower first odd sense amplifier **240A LO1** and the lower second odd sense amplifier **240A LO2**.

Individual sub-circuitry within a given sense amplifier section is represented in simplified form, both with functional acronyms and relative position. For example in the lower first odd sense amplifier **240A LO1** column select (CS) circuitry is centrally located with respect to the lower first odd sense amplifier **240A LO1** and the upper first odd sense amplifier **240A UO1**, and the CS sub-circuitry is distal from the boundaries of the first odd sense amplifier exit region **241A1**. Adjacent the CS sub-circuitry in the lower first odd sense amplifier **240A LO1**, is NMOS sense amplifier sub-circuitry (NSA), which is closer to the first odd sense amplifier exit region **241A1** than is the CS sub-circuitry. Adjacent the NSA is voltage transfer characteristic (VTC) sense amplifier sub-circuitry. Further and adjacent the VTC sense amplifier sub-circuitry is PMOS sense amplifier sub-circuitry (PSA). The balance of the first odd sense amplifier **240A LO1** is a “mirror image” repetition of sub-circuitry: PSA, VTC, and NSA to complete simplified sub-circuitry within the first odd sense amplifier **240A LO1**, where the second NSA is adjacent the first odd sense amplifier exit region **241A1**.

Lower lateral interconnects **199L** of the conductive routing structure assemblies, may each exit the first odd sense amplifier exit region **241A1**, and each lower lateral interconnect **199L** may couple to CS sub-circuitry within the respective lower first and second odd sense amplifiers **240A LO1** and **240A LO2**. Upper lateral interconnects **199U** may each exit the first odd sense amplifier exit region **241A1**, and each upper lateral interconnect **199U** may couple to CS circuitry within the respective upper first and second odd sense amplifiers **240A UO1** and **240A UO2**. In an embodiment, a given lower lateral interconnect **199L** has a shorter routing path (shorter length, shorter physical distance) at the K2 redistribution level (FIG. 4) from a digit line exit region **104** to the corresponding lower sense amplifier **240L**, than the corresponding upper lateral interconnect **199U** to the corresponding upper sense amplifier **240U**. Put another way, a given lower sense amplifier **240** may be connected at the K2 routing level from the contact pads of the third conductive routing structure assembly **301** of the conductive routing structure assemblies with a shorter routing distance with the lower lateral interconnect **199L** than the corresponding upper sense amplifier **240** is connected at the K2 routing level from the contact pads of the third conductive routing structure assembly **301** of the conductive routing structure assemblies by the upper lateral interconnect **199U**. In an embodiment, the CS circuitry for the lower sense amplifier **240L** is located closer to the sense amplifier exit region **241** than is the CS circuitry for the upper sense amplifier **240U**. In FIG. 6, the CS circuitries for adjacent lower and upper sense amplifiers, e.g., the lower first odd sense amplifier **240A LO1** and the upper first odd sense amplifier **240A UO1**, are substantially adjacent at proximate boundaries. In an embodiment, a single CS circuitry is located for each half cluster of sense amplifiers **240**, such that, e.g., the lower CS in the lower first odd sense amplifier **240A LO1** and the upper CS in the upper first odd sense amplifier **240A UO1** are configured as a single circuitry block. Even sense amplifiers **240B** may also be similarly arranged such that routing from the even sense amplifier exit regions **241B** is shorter to CS circuitry for lower even sense amplifiers **240B**

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than to upper even sense amplifiers **240B**. Similarly, in an embodiment, a single CS circuitry is located for each half cluster of sense amplifiers **240**, such that, e.g., the lower CS in a lower first even sense amplifier (not illustrated) and an upper CS in an upper first even sense amplifier (not illustrated) are configured as a single circuitry block.

FIG. 7 is a simplified top plan view of portions of a cluster of odd sense amplifiers **240A** for a configuration wherein lower and upper sense amplifiers **240** are clustered within a CMOS device (e.g., the third microelectronic device assembly **218** (FIG. 4)), in accordance with embodiments of the disclosure. In general, a portion of the general control logic circuitry **191** depicted in, e.g., FIG. 4, is specifically set forth as control logic circuitry **491** in FIG. 7. For clarity and simplicity, the sense amplifier cluster depicted in FIG. 7 is illustrated within a first array subregion **102A**, such as the first array subregion **102A** depicted in FIG. 4. In contrast with a single odd sense amplifier exit region **241A** (e.g., the first odd sense amplifier exit regions **241A1** depicted in FIGS. 5 and 6), the cluster of odd sense amplifiers **240A** includes two odd sense amplifier exit regions: a first paired first odd sense amplifier exit region **241A1A** and a second paired first odd sense amplifier exit region **241A1B**. For clarity and simplicity, in FIG. 7, it will be understood that features of the first paired first odd sense amplifier exit region **241A1A** and second paired first odd sense amplifier exit region **241A1B** are coupled to features of the first odd digit line exit region **104A1**, but no schematic coupling is given, in order to more clearly illustrate lower and upper lateral interconnects **199L** and **199U**. The interface contact pads of the third conductive routing structure assembly **301** (e.g., FIG. 4) are depicted schematically at boundaries of the first odd digit line exit region **104A1** at the K2 redistribution level (e.g., FIG. 4). The first lower odd sense amplifier **240A LO1** and the second lower odd sense amplifier **240A LO2** are paired between the first paired first odd sense amplifier exit region **241A1A** and the second paired first odd sense amplifier exit region **241A1B**. The first upper odd sense amplifier **240A UO1** and the upper second odd sense amplifier **240A UO2** are clustered peripherally to the respective first lower odd sense amplifier **240A LO1** and the second lower odd sense amplifier **240A LO2**.

Individual sub-circuitry within a given sense amplifier section is represented in simplified form, both with functional acronyms and relative position. For example in the lower first odd sense amplifier **240A LO1** column select (CS) circuitry is adjacent the boundaries of the first odd sense amplifier exit region **241A1**. Adjacent the CS circuitry in the lower first odd sense amplifier **240A LO1**, is NMOS sense amplifier sub-circuitry (NSA), and adjacent the NSA is voltage transfer characteristic (VTC) sense amplifier sub-circuitry. Further and adjacent the VTC sense amplifier sub-circuitry is PMOS sense amplifier sub-circuitry (PSA). The balance of the first odd sense amplifier **240A LO1** is a “mirror image” repetition of sub-circuitry: PSA, VTC, and NSA to complete simplified sub-circuitry within the first odd sense amplifier **240A LO1**. At the second occurrence of NSA sub-circuitry and distal from the first odd sense amplifier exit region **241A1**, an NSA sub-circuitry is represented within the lower second odd sense amplifier **240A LO2**.

Lower lateral interconnects **199L** may each exit the first paired first odd sense amplifier exit region **241A1A** and the second paired first odd sense amplifier exit region **241A1B**, and each lower lateral interconnect **199L** may couple to CS circuitry within the respective lower first and second odd sense amplifiers **240A LO1** and **240A LO2**. Upper lateral interconnects **199U** may each exit the first paired first odd

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sense amplifier exit region **241A1A** and the second paired first odd sense amplifier exit region **241A1B**, and each upper lateral interconnect **199U** may couple to CS circuitry within the respective upper first and second odd sense amplifiers **240A UO1** and **240A UO2**, which are peripherally clustered with the respective lower first and second odd sense amplifiers **240A LO1** and **240A LO2**. In an embodiment, a given lower lateral interconnect **199L** may have a shorter composite routing path (shorter length, shorter distance) from a digit line exit region **104** to CS circuitry than the corresponding composite routing path for an upper lateral interconnect **199U** to CS circuitry. Even sense amplifiers **240B** may also be similarly arranged as the odd sense amplifiers **240A** depicted in FIG. 7.

FIG. 8 is a simplified, partial longitudinal cross-section elevation view of the microelectronic device **101** that illustrates sub-word line driver (SWD) features of the microelectronic device **101**, according to several embodiments. The cross-section view is taken at an angle Y' to the second direction (X-directions) such as about 21 to illustrate both digit lines **118** and word lines **120** in cross section. The third microelectronic device assembly **218** is illustrated with the control logic circuitry **191**, SWD sections **242** of the control logic circuitry **191** and SA sections **240** of the control logic circuitry **191**. The SWD sections **242** include an odd SWD section **242A** within horizontal boundaries of the first array subregion **102A**, and another odd SWD section **242A** within horizontal boundaries of the third array subregion **102C**.

The illustrated view is orthogonal to the view depicted in FIG. 4, and several structures are identically enumerated. The longitudinal cross-section view of the microelectronic device **101** may be taken from the section line B in FIG. 3, where the longitudinal cross-section view includes the first array subregion **102A** for both the first microelectronic device assembly **156** and the second microelectronic device assembly **157**, the third array subregion **102C** also for both the first microelectronic device assembly **156** and the second microelectronic device assembly **157**, and portions of the third microelectronic device assembly **218** that are superimposed above the second microelectronic device assembly **157**. The longitudinal cross-section view illustrates odd sub-word line drivers **242A** in each of the first array subregion **102A** and the third array subregion **102C**, where the cut-away view bisects the first odd word line exit region **106A1** (FIG. 3) and the second odd word line exit region **106A2** (FIG. 3), where the odd sub-word line drivers **242A** appear on opposite sides of the respective first and second odd word line exit regions **106A1** and **106A2**, and with the cut-away view, the odd sub-word line driver sections **242A** also appear on opposite sides of the odd word line socket region **218AW** of the third microelectronic device assembly **218**.

Lateral (X-direction) boundaries may be defined at the level of the first microelectronic device assembly **156** and the second microelectronic device assembly **157**. Overall for the microelectronic device **101**, the odd word line exit region boundaries may be defined by an odd word line socket region **218AW**, that is within the third microelectronic device assembly **218** and located between the first array subregion **102A** and the third array subregion **102C**. Similarly overall for the microelectronic device **101**, the even word line exit region boundaries may be defined by an even word line socket region **218BW**, that is within the third microelectronic device assembly **218**, and adjacent left to the first array subregion **102A**.

Further for the first microelectronic device assembly **156** within the odd word line socket region **218AW**, the lateral

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boundaries may include a lower first odd word line socket region **156A LW1** for the first odd word line exit region **106A1** (FIG. 3, between the first array subregion **102A** and the third array subregion **102C**), and a lower second odd word line socket region **156A LW2** for the second odd word line exit region **106A2** (FIG. 3, between the first array subregion **102A** and the third array subregion **102C**). The lateral boundaries may be delineated by the base semiconductor material **110** and the dielectric material **114** that fills the lower first odd word line socket region **156A LW1** and the lower second odd word line socket region **156A LW2**. Similarly within the odd word line socket region **218AW**, lateral boundaries for the second microelectronic device assembly **157** may include an upper first odd word line socket region **156A UW1** for the first odd word line exit region **106A1**, and an upper second odd word line socket region **156A UW2** for the second odd word line exit region **106A2**. The lateral boundaries may be delineated by the base semiconductor material **111** and the dielectric material **115** that fills the upper first odd word line socket region **156A UW1** and the upper second odd word line socket region **156A UW2**.

Further for the first microelectronic device assembly **156** within the even word line socket region **218BW**, the lateral (X-direction) boundaries may include a lower second even word line socket region **156B LW2** for the second even word line exit region **106B2** (FIG. 3, adjacent left the first array subregion **102A**). The boundaries may be delineated by the base semiconductor material **110** and the dielectric material **114** that fills the lower second even word line socket region **156B LW2**. Similarly within the even word line socket region **218BW**, lateral boundaries for the second microelectronic device assembly **157** may include an upper second even word line socket region **156B UW2** for the second even word line exit region **106B2**. The boundaries may be delineated by the base semiconductor material **111** and the dielectric material **115** that fills the upper second even word line socket region **156B UW2**.

Further referring to FIG. 8 for clarity, the first microelectronic device assembly **156** is set forth in some detail at the third array subregion **102C**, and the first microelectronic device assembly **156** is set forth more generally at the first array subregion **102A**. Similarly, the second microelectronic device assembly **157** is set forth in some detail at the first array subregion **102A**, and the second microelectronic device assembly **157** is set forth more generally at the third array subregion **102C**.

In an embodiment for the first microelectronic device assembly **156**, the first base semiconductor structure **110** is the only semiconductor material in the first microelectronic device assembly **156**, such that an open architecture may permit different arrangements of odd word lines **120A** (FIG. 2B) enumerated, e.g., 1, 3, 5, 7 . . . (n+1), and even word lines **120B** (FIG. 2A), enumerated e.g., 0, 2, 4, 6 . . . n, where odd word lines **120A** (FIG. 2B) may extend from two horizontally neighboring array subregions **102** (FIG. 2B) into an odd word line exit region **106A** (FIG. 2B). The even word line exit regions **106B** (FIG. 2B) may extend from two other horizontally neighboring array subregions **102** (FIG. 2B) into an even word line exit region **106B** (FIG. 2B).

Within the word line exit region **106**, dummy digit lines **119** for the first microelectronic device assembly **156**, and dummy digit lines **219** for the second microelectronic device assembly **157**, may, optionally, be located vertically above the word lines **120**. If so located, the dummy digit lines **119** and **219** may be located at substantially the same vertical

position (e.g., vertical elevation) within the microelectronic device **101** (e.g., within the first base semiconductor structure **110** thereof for the first microelectronic device assembly **156**, and within the base structure thereof **111** for the second microelectronic device assembly **157**) as the digit lines **118**, and may be located to horizontally extend orthogonal to the word lines **120** (e.g., in the Y-direction). A material composition of the dummy digit lines **119** and **219** may be substantially the same as a material composition of the digit lines **118**. The dummy digit lines **119** and **219** may be electrically isolated from one another and the other components (e.g., the word lines **120**, the digit lines **118**) of the microelectronic device **101**. The dummy digit lines **119** and **219** (if any) within the word line exit region **106** may not be part of data paths during use and operation of the microelectronic device **101** of the disclosure. In additional embodiments, the dummy digit lines **119** and **219** are absent (e.g., omitted) from the word line exit regions **106**. In an embodiment, the dummy digit lines **119** and **219** may be located below the respective redistribution structure pads **299** (**K1**) and **301** (**K2**).

As shown in FIG. 8, sub-word line drivers (SWDs) of the SWD sections **242** and conductive structures coupling the word lines **120** to the sub-word line drivers of the SWD sections **242** may be coupled to digit line contacts **298**. SWD sections **242** may be proximately paired, with, e.g., a lower odd sub-word line driver **242A LO** (FIG. 3) and an upper odd sub-word line driver **242A UO** (FIG. 3) that are paired, and paired odd sub-word line drivers **242A** may each adjacent the odd word line socket region **281AW**.

Within an individual word line exit region **106**, conductive routing structure assemblies **297** may include a first redistribution structure pad **297** at a **K0** routing level coupled to an individual word line **120** by a first contact **295**. The first redistribution structure pad **297** (**K0**) may be part of a first conductive routing structure assembly coupled to a second conductive routing structure assembly including a second redistribution structure pad **299** (**K1**), where coupling is at least partially accomplished by a first word line interconnect **298W**. In an embodiment, the first redistribution structure pad **297** (**K0**) is at the same vertical level (**Z**-direction) as the first routing tier **134**, such that the first contact **295** extends between the first odd word line **120A** and the first redistribution structure pad **297** (**K0**), and such that the first contact **295** is vertically taller than illustrated. The first word line interconnect **298W** may also be referred to as a first “vertical word line contact” (**VWLCON**) **298W**. The second redistribution structure pad **299** (**K1**) may be part of a second conductive routing structure assembly located within the second routing tier **142** of the first microelectronic device assembly **156**. In addition, the third contact pad (**K2**) **301** may be part of the third conductive routing structure assembly vertically overlying and coupled to the second redistribution structure pad **299**. The third contact pad (**K2**) **301** may also be coupled to sub-word line driver circuitry within the SWD section **242**. The third contact pad (**K2**) **301** may be part of conductive routing structure assemblies positioned at an interface of the top isolation structure **235** formed from isolation materials **165** of the second microelectronic device assembly **157** and isolation materials **227** of the third microelectronic device assembly **218**; and the third contact pad (**K2**) **301** in the second microelectronic device assembly **157** may be bonded to the third microelectronic device assembly **218**. The third contact pad of the third conductive routing structure assembly **301** (**K2**) may also be referred to as a “top external contact pad **301**” (**K2**) (or top contact pad of the third

conductive routing structure assembly **301**) as the top contact pad of the third conductive routing structure assembly **301** (**K2**) may be at the upper boundary of the second microelectronic device assembly **157**, and the top contact pad of the third conductive routing structure assembly **301** may be registered, mated and bonded with electrical contacts **303** within the third microelectronic device assembly **218**. Similarly, the electrical contacts **303** may also be referred to as bottom contacts **303** (CMOS device bottom contacts **303**) of the third microelectronic device assembly **218**, where the bottom contacts **303** couple to the third contact pads (**K2**) **301** at the top isolation structure **235**. Still referring to FIG. 8, the conductive routing structure assemblies may include first conductive routing structure assemblies **297** that may include the first redistribution structure pad **297** (**K0**) within the first microelectronic device assembly **156**, second conductive routing structure assemblies **298** that may include the second redistribution structure pad **298** (**K1**) also within the first microelectronic device assembly **156**, and third conductive routing structure assemblies **301** that may include the third redistribution structure pad of the third conductive routing structure assembly **301** (**K2**) within the second microelectronic device assembly **157**.

Still referring to FIG. 8, electrical communication between the word lines **120** and sub-word line driver circuitry within the SWD sections **242** may be further accomplished by sub-word line driver contacts **305** that couples the sub-word line driver circuitry **242** to the CMOS device bottom contacts **303** (**K3**). In an embodiment, the first and third lower word line interconnects **298W1L** and **298W3L** are configured with a monolithic (single material, homogeneous characteristic electrically conductive) length (**Z**-direction) that extends at least between the combined height (**Z**-direction) of the digit lines **118**, the first routing structures **136**, and the storage node devices **138** within the first microelectronic device assembly **156**. Other electrical structures (e.g., conductive structures) may intervene between the lower word line interconnects, e.g., **298W1L** and the subsequent lower digit line contacts **298D1LS**. In an embodiment, the first and third upper word line interconnects **298W1U** and **298W3U** are configured with a monolithic (single material, homogeneous characteristic electrically conductive) length (**Z**-direction) that extends at least between the storage node devices **138** in the second microelectronic device assembly **157**.

FIG. 9 is a simplified plan view of a portion of the microelectronic device **101** including one of the digit line socket regions, such as the odd digit line socket region **218AD** depicted in FIG. 4, in accordance with embodiments of the disclosure. The odd digit line socket region **218AD** projects downwardly (**Z**-direction) into a digit line exit region **104** of the second microelectronic device assembly **157** and into a digit line exit region **104** of the first microelectronic device assembly **156**. An array of digit line contacts **298** is configured in a “socket out of array” arrangement where all the digit line contacts **298** are fully within given digit line exit regions, such as a lower first odd digit line exit region **104A1L** and an first upper odd digit line exit region **104A1U**, and the several digit line contacts **298** do not overlie any inactive word lines **120D** (also referred to as “dummy word lines” **120D**) as discussed further herein. The number of digit line contacts **298** is presented in simplified numbers and arrangements for clarity. Some of the digit lines **118** of the microelectronic device **101** are within the boundaries of one of the digit line exit regions **104**, and the associated sense amplifier sections **240** (e.g., FIG. 4) are accessed by the several odd digit lines **118A** by the digit line

contacts **298** within the digit line exit region **104**. Among the several digit lines **118** the first upper odd digit line **118A1U**, the first lower odd digit line **118A1L**, the third upper odd digit line **118A3U** and the third lower odd digit line **118A3L** taken from FIG. 4 are highlighted. Several upper odd digit lines **118AU** and several lower odd digit lines **118AL** are also enumerated. The lower odd digit lines **118AL** are seen from the first microelectronic device assembly **156** (e.g., FIG. 4) and the upper odd digit lines **118AU** are seen from the second microelectronic device assembly **157** (e.g., FIG. 4). The several digit line contacts **298** have a first population density within the area of the first microelectronic device assembly **156**, and the several digit line contacts **298** have a second population density within the area of the second microelectronic device assembly **157** where the second population density may be double the first population density.

The first lower digit line interconnect **298D1L** contacts the first lower odd digit line **118A1L**. The second redistribution structure pad **299** (**K1**) contacts the first lower digit line interconnect **298D1L**, and the third redistribution layer of the third conductive routing structure assembly **301** (**K2**), which is illustrated semi-translucently to illustrate directly below located lower structures. The third lower digit line interconnect **298D3L** contacts the third lower odd digit line **118A3L**. The second redistribution structure pad **299** (**K1**) contacts the third lower digit line interconnect **298D3L**, and the third redistribution layer of the third conductive routing structure assembly **301** (**K2**), which is illustrated semi-translucently to illustrate directly lower structures.

In an embodiment as illustrated, e.g., the first lower odd digit line **118A1L** extends continuously between the first array subregion **102A** and the second array subregion **102B**. In an embodiment, the first lower odd digit line **118A1L** extends only from one of the first array subregion **102A** and the second array subregion **102B**, such that the first lower odd digit line **118A1L** terminates at the lower first digit line interconnect **289D1L**. Another lower odd digit line **118AL** extends from the other of the first array subregion **102A** and the second array subregion **102B**, and terminates at a different digit line interconnect **298DL**. Such termination configurations may, for example, be employed to provide more space for contacts (e.g., the first contact **295** (FIG. 8) for word lines **120**) and conductive routing structure assemblies, such as the redistribution structures (e.g., first redistribution structure pad (**K0**) **297**, FIG. 4) operatively associated with at least some of the odd word lines **120A** within the odd word line exit region **106A**.

FIG. 10 is a simplified plan view of a portion of a digit line exit region **104** of a microelectronic device **201**, wherein distribution of some electrical interconnects **298** between digit lines **118** and sense amplifiers **240** (FIG. 4) are arranged in a configuration of “halfway distributed,” in accordance with additional embodiments of the disclosure. The “halfway distributed” configuration shown in FIG. 10 is different than the “socket out of array” configuration previously described with reference to FIG. 9 (wherein all electrical interconnects or digit line contacts **298** are within the socket area). Similar to the configuration in FIG. 8, one of the digit line socket regions is illustrated, such as the odd digit line socket region **218AD** depicted in FIG. 4, and projects downwardly (Z-direction) into a digit line exit region **104** of the second microelectronic device assembly **157** and into a digit line exit region **104** of the first microelectronic device assembly **156** according to several embodiments. An array of digit line contacts **298** is configured in the “halfway distributed” arrangement where half the

digit line contacts **298** are fully within a given digit line exit region such as the first lower odd digit line exit region **104A1L** or the first upper odd digit line exit region **104A1U** (the left illustrated half of digit line contacts), and about half the several digit line contacts **298** at least partially overlie inactive word lines **120D**, as discussed further herein. The digit line contacts **298** include upper digit line contacts, e.g., first upper digit line contact **298D1U**, lower digit line contacts, e.g., first lower digit line contact **298D1L**, and subsequent lower digit line contact **298D1LS** (FIGS. 4 and 8). Detail for each of the third upper odd digit line **118A3U** and the third lower odd digit line **118A3L**, include connection to respective upper and lower digit line contacts **298D3U** and **298D3L**. Other connections are also illustrated for each of the third upper odd digit line **118A3U** and the third lower odd digit line **118A3L**, including coupling to the second redistribution structure pad **299** (**K1**) and to the third redistribution structure of the third conductive routing structure assembly **301** (**K3**).

Half of the digit line contacts **298** of the microelectronic device **201** may be peripheral to or adjacent to the boundaries of one of the digit line exit regions **104**, and the associated sense amplifier sections **240** (e.g., FIG. 4) may be accessed by the several odd digit lines **118A** by the digit line contacts **298** peripheral to or adjacent to the boundaries of the digit line exit regions **104**. Among the several digit lines **118**, the first upper odd digit line **118A1U** and the first lower odd digit line **118A1L** may be coupled to halfway distributed conductive routing structure assemblies that are peripheral to or adjacent to the illustrated right boundaries of the digit line exit regions **104**.

For the first upper odd digit line **118A1U**, the second redistribution structure pad **299** (**K1**) may include a **K1** trace portion **299T** coupled to the first upper digit line contact **298D1U**, where the first upper digit line contact **298D1U** and the third redistribution layer contact of the third conductive routing structure assembly **301** (**K2**) may be at least partially above electrically inactive word lines **120D** within the second array subregion **102B**. The second redistribution structure pad **299** (**K1**) may contact the first upper digit line contact **298D1U**. The trace portion **299T** may extend to and contact the subsequent upper digit line contact **298D1US**. The subsequent upper digit line contact **298D1US** may contact the third redistribution layer of the third conductive routing structure assembly **301** (**K2**), which is illustrated semi-translucently to illustrate directly below located lower structures.

Similarly for the first lower odd digit line **118A1L**, a first lower digit line contact **298D1L** may be coupled to the second redistribution structure pad **299** (**K1**), and the second redistribution structure pad **299** may include a trace portion **299T** coupled to the subsequent lower digit line contact **298D1LS**. The subsequent lower digit line contact **298D1LS** and the third redistribution layer contact of the third conductive routing structure assembly **301** (**K3**) may be at least partially above the electrically inactive word lines **120D** within the second array subregion **102B**. The first lower digit line interconnect **298D1L**, may contact the first lower odd digit line **118A1L**. The second redistribution structure pad **299** (**K1**) may contact the first lower digit line interconnect **298D1L**. The trace portion **299T** may extend to and contact the subsequent lower digit line contact **298D1LS**. The subsequent lower digit line contact **298D1LS** may contact the third redistribution layer of the third conductive routing structure assembly **301** (**K2**), which is illustrated semi-translucently to illustrate directly below located lower structures. Contact pads of the third redistribution layer of the

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third conductive routing structure assembly **301** may be part of conductive routing structure assemblies at the K2 level within the second microelectronic device assembly **157**.

Processing of the several structures for the microelectronic device includes forming array regions **102**, digit line exit regions **104**, word line exit regions **106**, access devices **116** and supporting structures, storage node devices **138** and supporting structures, and CMOS devices **218** among other processing. Processing also include joining the first microelectronic device assembly **156** to the second microelectronic device assembly **157**, and further joining the “folded memory arrays” of the first microelectronic device assembly **156** and the second microelectronic device assembly **157** to the CMOS device that is part of the third microelectronic device assembly **218**.

FIGS. 11A through 11C illustrate simplified, partial longitudinal cross-sectional views of different regions of a microelectronic device precursor structure **100** during assembly to achieve the microelectronic device **101** previously described with reference to FIGS. 1 through 10, in accordance with embodiments of the disclosure. FIG. 11A illustrates a simplified, partial longitudinal cross-sectional view from the perspective of the Y-direction (so as to depict an XZ-plane) of one of the array subregions **102** (e.g., the first array subregion **102A**) of microelectronic device **101** shown in FIG. 1. FIG. 11B illustrates a simplified, partial longitudinal cross-sectional view from the perspective of the Y-direction (so as to depict an XZ-plane) of one of the digit line exit regions **104** of the microelectronic device **101** shown in FIG. 1. FIG. 11C illustrates a simplified, partial longitudinal cross-sectional view from the perspective of the X-direction (so as to depict an YZ-plane) of one of the word line exit regions **106** of the microelectronic device **101** shown in FIG. 1.

Referring collectively to FIGS. 11A through 11C, the first microelectronic device precursor structure **100** may be formed to include the first base semiconductor structure **110**, filled trenches **112**, and a first isolation material **114**. The filled trenches **112** vertically extend (e.g., in the Z-direction) into the first base semiconductor structure **110**. The first isolation material **114** covers and surrounds surfaces of the first base semiconductor structure **110**.

The first base semiconductor structure **110** comprises a base material or construction upon which additional features (e.g., materials, structures, devices) of the microelectronic device precursor structure **100** are formed. The first base semiconductor structure **110** may comprise a semiconductor structure (e.g., a semiconductor wafer), or a base semiconductor material on a supporting structure. For example, the first base semiconductor structure **110** may comprise a conventional silicon substrate (e.g., a conventional silicon wafer), or another bulk substrate comprising a semiconductor material. In some embodiments, the first base semiconductor structure **110** comprises a silicon wafer. The first base semiconductor structure **110** may include one or more layers, structures, and/or regions formed therein and/or thereon.

The filled trenches **112** may comprise trenches (e.g., openings, vias, apertures) within the first base semiconductor structure **110** that are at least partially (e.g., substantially) filled with the first isolation material **114**. The filled trenches **112** may, for example, be employed as shallow trench isolation (STI) structures within the first base semiconductor structure **110**. The filled trenches **112** may be formed to vertically extend partially (e.g., less than completely) through the first base semiconductor structure **110**. Each of the filled trenches **112** may be formed to exhibit substan-

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tially the same dimensions and shape as each other of the filled trenches **112**, or at least one of the filled trenches **112** may be formed to exhibit one or more of different dimensions and a different shape than at least one other of the filled trenches **112**. As a non-limiting example, each of the filled trenches **112** may be formed to exhibit substantially the same vertical dimension(s) and substantially the same vertical cross-sectional shape(s) as each other of the filled trenches **112**; or at least one of the filled trenches **112** may be formed to exhibit one or more of different vertical dimension(s) and different vertical cross-sectional shape(s) than at least one other of the filled trenches **112**. The first isolation material **114** may be formed of and include at least one insulative material. By way of non-limiting example, the first isolation material **114** may be formed of and include one or more of at least one dielectric oxide material (e.g., one or more of SiO_x , phosphosilicate glass, borosilicate glass, borophosphosilicate glass, fluorosilicate glass, AlO_x , HfO_x , NbO_x , and TiO_x), at least one dielectric nitride material (e.g., SiN_y), at least one dielectric oxynitride material (e.g., SiO_xN_y), at least one dielectric carboxynitride material (e.g., $\text{SiO}_x\text{C}_z\text{N}_y$), and amorphous carbon. In some embodiments, the first isolation material **114** is formed of and includes SiO_x (e.g., SiO_2). The first isolation material **114** may be substantially homogeneous, or the first isolation material **114** may be heterogeneous. In some embodiments, the first isolation material **114** is substantially homogeneous. In additional embodiments, the first isolation material **114** is heterogeneous. The first isolation material **114** may, for example, be formed of and include a stack of at least two different dielectric materials.

Referring next to FIGS. 12A through 12C, illustrated are simplified, partial longitudinal cross-sectional views, from the directional perspectives previously described, of the array subregion **102** (FIG. 12A), the digit line exit region **104** (FIG. 12B), and the word line exit region **106** (FIG. 12C) at a processing stage of the method of forming the microelectronic device **101** following the processing stage described with reference to FIGS. 11A through 11C. As collectively depicted in FIGS. 12A through 12C, access devices **116** (FIG. 12A) (e.g., access transistors) may be formed within the array subregion **102** (FIG. 12A). In addition, digit lines **118** (FIGS. 12A and 12B) (e.g., data lines, bit lines) may be formed to be coupled to the access devices **116** (FIG. 12A) and to horizontally extend in the Y-direction through the array subregion **102** (FIG. 12A). At least some of the digit lines **118** (FIGS. 12A and 12B) may terminate (e.g., end) within the digit line exit region **104** (FIG. 12B). Furthermore, word lines **120** (e.g., access lines) may be formed to be coupled to the access devices **116** (FIG. 12A) and to horizontally extend in the X-direction through the array subregion **102** (FIG. 3A). At least some of the word lines **120** (FIGS. 12A and 12C) may terminate within the word line exit region **106** (FIG. 12C).

Referring to FIG. 12A, the access devices **116** formed within the array subregion **102** may be employed as components of memory cells (e.g., DRAM cells) to be formed within the array subregion **102**. By way of non-limiting example, each access device **116** may individually be formed to include a channel region comprising a portion of the first base semiconductor structure **110**; a source region and a drain region each individually comprising one or more of at least one conductively doped portion of the first base semiconductor structure **110** and/or at least one conductive structure formed in, on, or over the first base semiconductor structure **110**; and at least one gate structure comprising a portion of at least one of the word lines **120**. Each access

device **116** may also include a gate dielectric material (e.g., a dielectric oxide material) formed to be interposed between the channel region thereof and the gate structure thereof.

The digit lines **118** may exhibit horizontally elongate shapes extending in parallel in the Y-direction; and the word lines **120** may exhibit horizontally elongate shapes extending in parallel in the X-direction orthogonal to the Y-direction. As used herein, the term “parallel” means substantially parallel. The digit lines **118** and the word lines **120** may each individually be formed of and include conductive material. By way of non-limiting example, the digit lines **118** and the word lines **120** may each individually be formed of and include one or more of at least one metal, at least one alloy, and at least one conductive metal-containing material (e.g., a conductive metal nitride, a conductive metal silicide, a conductive metal carbide, a conductive metal oxide). In some embodiments, the digit lines **118** and the word lines **120** are each individually formed of and include one or more of W, Ru, Mo, and titanium nitride (TiN_x). Each of the digit lines **118** and each of the word lines **120** may individually be substantially homogeneous, or one or more of the digit lines **118** and/or one or more of the word lines **120** may individually be substantially heterogeneous. In some embodiments, each of the digit lines **118** and each of the word lines **120** are formed to be substantially homogeneous.

Still referring to FIG. 12A, within the array subregion **102**, additional features (e.g., structures, materials) are also formed on, over, and/or between the access devices **116**, the digit lines **118**, and the word lines **120**. For example, as shown in FIG. 12A, first contact structures **122** (e.g., digit line contact structures, also referred to as so-called “bitcon” structures) may be formed to vertically extend between and couple the access devices **116** to the digit lines **118**; second contact structures **124** (e.g., cell contact structures, also referred to as so-called “cellcon” structures) may be formed in contact with the access devices **116** and may be configured and positioned to couple the access devices **116** to subsequently formed storage node devices (e.g., capacitors); dielectric cap structures **126** may be formed on or over the digit lines **118**; and additional dielectric cap structures **128** may be formed on or over the word lines **120**. In addition, dielectric structures (e.g., dielectric spacers, such as low-k dielectric spacers formed of and including one or more low-k dielectric materials) may be formed to intervene (e.g., horizontally intervene) between and isolate the second contact structures **124** and digit lines **118**; and further dielectric structures (e.g., gate dielectric structures, such as gate dielectric oxide structures) may be formed to intervene (e.g., horizontally intervene) between and isolate the first contact structures **122** and the word lines **120**.

The first contact structures **122** and the second contact structures **124** may individually be formed of and include at least one conductive material. In some embodiments, the first contact structures **122** and the second contact structures **124** are individually formed of and include one or more of at least one metal (e.g., W), at least one alloy, at least one conductive metal silicide (e.g., one or more of titanium silicide (TiSi_x), cobalt silicide (CoSi_x), tungsten silicide (WSi_x), tantalum silicide (TaSi_x), molybdenum silicide (MoSi_x), and nickel silicide (NiSi_x)), and at least one conductive metal nitride (e.g., one or more of TiN_x, tungsten nitride (WN_x), tantalum nitride (TaN_x), cobalt nitride (CoN_x), molybdenum nitride (MoN_x), and nickel nitride (NiN_x)). In addition, the dielectric cap structures **126** and the additional dielectric cap structures **128** may individually be formed of and include at least one insulative material. In some embodiments, the dielectric cap structures **126** and the

additional dielectric cap structures **128** are individually formed of and include a dielectric nitride material (e.g., SiN_x, such as Si₃N₄).

Referring to FIG. 12B, within the digit line exit region **104**, at least some of the digit lines **118** may horizontally terminate (e.g., end) in the Y-direction. Each of the digit lines **118** horizontally extending through the array subregion **102** (FIG. 12A) and horizontally terminating within the digit line exit region **104** may be formed to terminate at substantially the same horizontal position in the Y-direction; or at least one of the digit lines **118** horizontally terminating within the digit line exit region **104** may be formed to terminate at a different horizontal position in the Y-direction within the digit line exit region **104** than at least one other of the digit lines **118** horizontally terminating within the digit line exit region **104**. In some embodiments, at least some digit lines **118** horizontally neighboring one another in the X-direction have terminal ends (e.g., terminal surfaces) horizontally offset from one another in the Y-direction. Horizontally offsetting the terminal ends of some of the digit lines **118** from the terminal ends of some other of the digit lines **118** within the digit line exit region **104** may, for example, promote or facilitate desirable contact structure arrangements within the digit line exit region **104**.

As shown in FIG. 12B, within the digit line exit region **104**, dummy word lines **121** may, optionally, be formed vertically below the digit lines **118**. If formed, the dummy word lines **121** may be formed at substantially the same vertical position (e.g., vertical elevation) within the first microelectronic device precursor structure **100** (e.g., within the first base semiconductor structure **110** thereof) as the word lines **120** (FIGS. 12A and 12C), and may be formed to horizontally extend orthogonal to the digit lines **118** (e.g., in the X-direction). A material composition of the dummy word lines **121** may be substantially the same as a material composition of the word lines **120** (FIGS. 12A and 12C). If formed, the dummy word lines **121** may be electrically isolated from one another and the other components (e.g., the word lines **120** (FIGS. 12A and 12C), the digit lines **118**) of the first microelectronic device precursor structure **100**. The dummy word lines **121** (if any) within the digit line exit region **104** may not be part of data paths during use and operation of a microelectronic device formed through the methods of the disclosure. In additional embodiments, the dummy word lines **121** are absent (e.g., omitted) from the digit line exit region **104**.

Referring next to FIG. 12C, within the word line exit region **106**, at least some of the word lines **120** may horizontally terminate (e.g., end) in the X-direction. Each of the word lines **120** horizontally extending through the array subregion **102** (FIG. 12A) and horizontally terminating within the word line exit region **106** may be formed to terminate at substantially the same horizontal position in the X-direction; or at least one of the word lines **120** horizontally terminating within the word line exit region **106** may be formed to terminate at a different horizontal position in the X-direction within the word line exit region **106** than at least one other of the word lines **120** horizontally terminating within the word line exit region **106**. In some embodiments, at least some word lines **120** horizontally neighboring one another in the Y-direction have terminal ends (e.g., terminal surfaces) horizontally offset from one another in the X-direction. Horizontally offsetting the terminal ends of some of the word lines **120** from the terminal ends of some other of the word lines **120** within the word line exit region **106** may, for example, promote or facilitate desirable contact structure arrangements within the word line exit region **106**.

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As shown in FIG. 12C, within the word line exit region 106, dummy digit lines 119 may, optionally, be formed vertically above the word lines 120. If formed, the dummy digit lines 119 may be formed at substantially the same vertical position (e.g., vertical elevation) within the first microelectronic device precursor structure 100 (e.g., within the second isolation material 130 thereof) as the digit lines 118 (FIGS. 12A and 12B), and may be formed to horizontally extend orthogonal to the word lines 120 (e.g., in the Y-direction). A material composition of the dummy digit lines 119 may be substantially the same as a material composition of the digit lines 118 (FIGS. 12A and 12B). If formed, the dummy digit lines 119 may be electrically isolated from one another and the other components (e.g., the digit lines 118 (FIGS. 12A and 12B), the word lines 120) of the first microelectronic device precursor structure 100. The dummy digit lines 119 (if any) within the word line exit region 106 may not be part of data paths during use and operation of a microelectronic device formed through the methods of the disclosure. In additional embodiments, the dummy digit lines 119 are absent (e.g., omitted) from the word line exit region 106.

Referring collectively to FIGS. 12A through 12C, the second isolation material 130 may be formed on or over portions of at least the first base semiconductor structure 110, the access devices 116 (FIG. 12A), the digit lines 118 (FIGS. 12A and 12B), the word lines 120 (FIGS. 12A and 12C), the second contact structures 124, and the first isolation material 114. The second isolation material 130 may be formed of and include at least one insulative material. A material composition of second isolation material 130 may be substantially the same as a material composition of the first isolation material 114, or the material composition of the second isolation material 130 may be different than the material composition of the first isolation material 114. In some embodiments, the second isolation material 130 is formed of and includes a dielectric oxide material, such as SiO_x (e.g., SiO_2). The second isolation material 130 may be substantially homogeneous, or the second isolation material 130 may be heterogeneous. In some embodiments, the second isolation material 130 is substantially homogeneous. In additional embodiments, the second isolation material 130 is heterogeneous. The second isolation material 130 may, for example, be formed of and include a stack of at least two different dielectric materials.

After assembly of the microelectronic device precursor structure 100 depicted in FIGS. 12A through 12C, further processing includes forming at least some of the first routing structures 136 of the first routing tier 134 (FIGS. 4 and 8), and further coupling the access devices 116 to the storage node devices 138 (e.g., capacitors) to form memory cells 146 (FIGS. 4 and 8) within the array subregion 102. Each memory cell 146 may individually include one of the access devices 116; one of the storage node devices 138; one of the second contact structures 124 interposed between the access device 116 and the storage node device 138; and one of the first routing structures 136 interposed between the second contact structure 124 and the storage node device 138. At least some of the first routing structures 136 within the array subregion 102 may, for example, be configured and employed as redistribution material (RDM) structures (also referred to as “redistribution layer” (RDL) structures) to effectively shift (e.g., stagger, adjust, modify) lateral positions of semiconductor pillars of the access devices 116 to accommodate a desired arrangement (e.g., a hexagonal close packed arrangement) of the storage node devices 138 (FIGS. 4 and 8) vertically over and in electrical communication

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with the access devices 116. At least some of the first routing structures 136 within at least one of the first routing tiers 134 may be coupled to at least some of the first routing structures 136 within at least one other of the first routing tiers 134 by way of conductive interconnect structures.

Referring to again to FIGS. 4 and 8, within the array subregion 102, the storage node devices 138 may individually be formed and configured to store a charge representative of a programmable logic state of the memory cell 146 including the storage node device 138. In some embodiments, the storage node devices 138 comprise capacitors. During use and operation, a charged capacitor may represent a first logic state, such as a logic 1; and an uncharged capacitor may represent a second logic state, such as a logic 0. Each of the storage node devices 138 may, for example, be formed to include a first electrode (e.g., a bottom electrode), a second electrode (e.g., a top electrode), and a dielectric material between the first electrode and the second electrode.

FIG. 13 illustrates a simplified, partial longitudinal cross-sectional view of the method of forming the microelectronic device following the processing stage of FIGS. 12A through 12C, in accordance with embodiments of the disclosure. A microelectronic device precursor structure 200 constituting a portion of the second microelectronic device assembly 157 (FIGS. 4 and 8) may be partially fabricated and bonded to the first microelectronic device assembly 156 (not illustrated in FIG. 13). After fabricating a portion of a second microelectronic device precursor structure 257, fabrication of the second microelectronic device precursor structure 257 is further accomplished, before attaching (e.g., bonding) the second microelectronic device assembly (e.g., the second microelectronic device assembly 157 in FIGS. 4 and 8) to a third microelectronic device assembly, such as the third microelectronic device assembly 218 depicted in part in FIG. 8. A microelectronic device precursor structure 200 may be a portion of the second microelectronic device precursor structure 257 processed before assembling the first routing structures 136 (FIG. 12A) and completing the storage node devices 138 (FIGS. 4 and 8) that are part of the arrays of memory cells 146 for the second microelectronic device assembly 157 (FIGS. 4 and 8). The processing may include mating a carrier wafer 310 to the microelectronic device precursor structure 200 through a sacrificial oxide layer 350, inverting the microelectronic device precursor structure 200, back grinding the base semiconductor structure 110 to form the trench isolation material 113, and then forming the isolation materials 226 (FIGS. 4 and 8) for bonding the second microelectronic device precursor structure 257 to the first microelectronic device assembly 156 (FIGS. 4 and 8). After bonding (e.g., oxide-oxide bonding) the second microelectronic device precursor structure 257 to the first microelectronic device assembly 156, further processing may be effectuated to fabricate the storage node devices 138 (FIGS. 4 and 8) that are part of the arrays of memory cells 146, among other structures of the second microelectronic device assembly 157 (FIGS. 4 and 8). Processing by this embodiment mitigates the risk of damage to the storage node devices 138 that are part of the arrays of memory cells 146 by assembling the storage node devices 138 effectuating the processing conduction (e.g., temperatures) needed to attach (e.g., bond) the first microelectronic device assembly 156 to the second microelectronic device precursor structure 257.

FIG. 14 illustrates a simplified, partial longitudinal cross-sectional view of the array subregion 102 at a processing

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stage of the method of forming the microelectronic device following the processing stage of FIGS. 12A through 12C, in accordance with embodiments of the disclosure. A third microelectronic device precursor structure 318 may be processed before completion of CMOS devices of the third microelectronic device assembly 218 (FIGS. 4 and 8). After fabricating a portion of the third microelectronic device precursor structure 318, fabrication of the third microelectronic device assembly 218 (FIGS. 4 and 8) is further accomplished, before attaching (e.g., bonding) to the second microelectronic device assembly 157. A microelectronic device precursor structure 300 may be a portion of the third microelectronic device assembly 218 (FIGS. 4 and 8). The illustrated microelectronic device precursor structure 300 of the third microelectronic device assembly 218 may be processed from the third microelectronic device precursor structure 318. The processing may include mating a carrier wafer 410 to the microelectronic device precursor structure 300 through a sacrificial oxide layer 450, inverting the microelectronic device precursor structure 300, back grinding base semiconductor structure 311 to form trench isolation material 315, followed by forming the isolation materials 227 (FIGS. 4 and 8) for bonding the second microelectronic device assembly 157 to the third microelectronic device precursor structure 318 to form the third microelectronic device assembly 218 (FIGS. 4 and 8). After bonding (e.g., oxide-oxide bonding) the third microelectronic device precursor structure 318 to the second microelectronic device assembly 157 (FIGS. 4 and 8), further processing may be accomplished to fabricate back-end-of-line (BEOL) metallization, such as bonding pads 202 (FIGS. 4 and 8), to structures, such as bond pad structures 198 (FIGS. 4 and 8).

Microelectronic devices (e.g., the microelectronic device 101) of the disclosure may be used in embodiments of electronic systems of the disclosure. For example, FIG. 15 is a block diagram of an electronic system 1500, according to embodiments of disclosure. The electronic system 1500 may comprise, for example, a computer or computer hardware component, a server or other networking hardware component, a cellular telephone, a digital camera, a personal digital assistant (PDA), portable media (e.g., music) player, a Wi-Fi or cellular-enabled tablet such as, for example, an iPad® or SURFACE® tablet, an electronic book, or a navigation device, etc. The electronic system 1500 includes at least one memory device 1520. The memory device 1520 may include, for example, one or more of the microelectronic devices (e.g., the microelectronic device 101) of the disclosure. The electronic system 1500 may further include at least one electronic signal processor device 1510 (often referred to as a “microprocessor”) that is part of an integrated circuit. The electronic signal processor device 1510 may include, for example, one or more of microelectronic device (e.g., the microelectronic device 101) of the disclosure. While the memory device 1520 and the electronic signal processor device 1510 are depicted as two (2) separate devices in FIG. 15, in additional embodiments, a single (e.g., only one) memory/processor device having the functionalities of the memory device 1520 and the electronic signal processor device 1510 is included in the electronic system 1500. In such embodiments, the memory/processor device may include, for example, one or more of the microelectronic devices (e.g., the microelectronic device 101) of the disclosure. The electronic signal processor device 1510 and the memory device 1520 may be part of a disaggregated-die assembly 1510 and 1520. The disaggregated-die assembly may be coupled among the electronic

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signal processor device 1510 and the memory device 1520 by an embedded multi-die silicon bridge.

The electronic system 1500 may further include one or more input devices 1530 for inputting information into the electronic system 1500 by a user, such as, for example, a mouse or other pointing device, a keyboard, a touchpad, a button, or a control panel. The electronic system 400 may further include one or more output devices 1540 for outputting information (e.g., visual or audio output) to a user such as, for example, a monitor, a display, a printer, an audio output jack, and/or a speaker. In some embodiments, the input device 430 and the output device 1540 may comprise a single touchscreen device that can be used both to input information to the electronic system 1500 and to output visual information to a user. The input device 1530 and the output device 1540 may communicate electrically with one or more of the memory device 1520 and the electronic signal processor device 1510.

Thus, disclosed is a microelectronic device, comprising a control logic structure including sense amplifiers clustered around sense amplifier exit regions; an upper memory array structure underlying the control logic structure and comprising memory cells coupled to some of the sense amplifiers of the control logic structure by way of routing extending through the sense amplifier exit regions; and a lower memory array structure underlying the upper memory array structure and comprising additional memory cells coupled to some other of the sense amplifiers of the control logic structure by way of additional routing extending through the sense amplifier exit regions.

Also disclosed is a microelectronic device, comprising a first memory array structure comprising: first array regions individually including first memory cells; first digit lines coupled to the first memory cells of the first array regions and extending in a first direction, at least some of the first digit lines terminating within digit line exit regions alternating with the first array regions in the first direction; and first word lines coupled to the first memory cells of the first array regions and extending in a second direction orthogonal to the first direction, at least some of the first word lines terminating within word line exit regions alternating with the first array regions in the second direction; a second memory array structure vertically overlying the first memory array structure and comprising: second array regions individually including second memory cells; second digit lines coupled to the second memory cells of the second array regions and extending in the first direction, at least some of the second digit lines terminating within the digit line exit regions; and second word lines coupled to the second memory cells of the second array regions and extending in the second direction, at least some of the second word lines terminating within the word line exit regions; and a control logic structure vertically overlying the second memory array structure and comprising: first sense amplifiers coupled to the first digit lines; second sense amplifier coupled to the second digit lines; first sub-word line drivers coupled to the first word lines; and second sub-word line drivers coupled to the second word lines.

Also disclosed is an electronic system, comprising: an input device; an output device; a processor device operably coupled to the input device and the output device; and a memory device operably coupled to the processor device and comprising at least one microelectronic device structure comprising: a control logic device structure comprising: sense amplifiers horizontally neighboring sense amplifier exit regions; sub-word line drivers horizontally offset from the sense amplifiers; a first microelectronic device structure

vertically underlying the control logic device structure and including memory cells coupled to some of the sense amplifiers by way of conductive structures extending from the some of the memory cells and through the sense amplifier exit regions; and a second microelectronic device structure vertically interposed between the first microelectronic device structure and the control logic device structure, the second microelectronic device structure including additional memory cells coupled to some other of the sense amplifiers by way of additional conductive structures extending from the additional memory cells and through sense amplifier exit regions.

The structures, devices, system, and methods of the disclosure advantageously facilitate one or more of improved microelectronic device performance, reduced costs (e.g., manufacturing costs, material costs), increased miniaturization of components, and greater packaging density as compared to conventional structures, conventional devices, conventional systems, and conventional methods. The structures, devices, systems, and methods of the disclosure may also improve scalability, efficiency, and simplicity as compared to conventional structures, conventional devices, conventional systems, and conventional methods.

While the disclosure is susceptible to various modifications and alternative forms, specific embodiments have been shown by way of example in the drawings and have been described in detail herein. However, the disclosure is not limited to the particular forms disclosed. Rather, the disclosure is to cover all modifications, equivalents, and alternatives falling within the scope of the following appended claims and their legal equivalents. For example, elements and features disclosed in relation to one embodiment of the disclosure may be combined with elements and features disclosed in relation to other embodiments of the disclosure.

What is claimed is:

1. A microelectronic device, comprising:

a control logic structure including sense amplifiers clustered around sense amplifier exit regions;

an upper memory array structure underlying the control logic structure and comprising memory cells coupled to some of the sense amplifiers of the control logic structure by way of routing extending through the sense amplifier exit regions; and

a lower memory array structure underlying the upper memory array structure and comprising additional memory cells coupled to some other of the sense amplifiers of the control logic structure by way of additional routing extending through the sense amplifier exit regions.

2. The microelectronic device of claim 1, wherein: the some other of the sense amplifiers comprise lower sense amplifiers paired adjacent and across the sense amplifier exit regions; and

the some of the sense amplifiers comprise upper sense amplifiers adjacent the lower sense amplifiers more distal from the sense amplifier exit regions than the lower sense amplifiers.

3. The microelectronic device of claim 2, wherein:

the upper memory array structure comprises:

array regions including the memory cells within horizontal areas thereof;

digit lines coupled to the memory cells and extending in a first direction;

word lines coupled to the memory cells and extending in a second direction orthogonal to the first direction;

digit line exit regions horizontally alternating with the array regions in the first direction, the digit lines

extending into the digit line exit regions and coupled to the routing by way of first contact structure within the digit line exit regions;

word line exit regions horizontally alternating with the array regions in the second direction; and

the lower memory array structure comprises:

additional array regions including the additional memory cells within horizontal areas thereof;

additional digit lines coupled to the additional memory cells and extending in the first direction;

additional word lines coupled to the additional memory cells and extending in the second direction;

additional digit line exit regions horizontally alternating with the additional array regions in the first direction, the additional digit lines extending into the additional digit line exit regions and coupled to the additional routing by way of second contact structure within the additional digit line exit regions; and additional word line exit regions horizontally alternating with the array regions in the second direction.

4. The microelectronic device of claim 2, wherein:

the sense amplifier exit regions further comprise:

odd sense amplifier exit regions; and

even sense amplifier exit regions;

the lower sense amplifiers comprise:

lower odd sense amplifiers paired adjacent and across the odd sense amplifier exit regions; and

lower even sense amplifiers paired adjacent and across the even sense amplifier exit regions; and

the upper sense amplifiers comprise:

upper odd sense amplifiers adjacent the lower odd sense amplifiers and spaced from the odd sense amplifier exit regions by the lower odd sense amplifiers; and

upper even sense amplifiers the lower even sense amplifiers and spaced from the even sense amplifier exit regions by the lower even sense amplifiers.

5. The microelectronic device of claim 4, wherein:

the lower memory array structure comprises lower odd first digit lines and lower odd third digit lines individually coupled to the lower odd sense amplifiers; and the upper memory array structure comprises upper odd first digit lines and upper odd third digit lines individually coupled to the upper odd sense amplifiers.

6. The microelectronic device of claim 5, wherein:

the lower odd first digit lines, lower odd second digit lines, the lower odd third digit lines, and lower odd fourth digit lines are coupled through contact structures within lower odd first and second digit line exit regions of the lower memory array structure to the lower odd sense amplifiers; and

the upper odd first digit lines, upper odd second digit lines, the upper odd third digit lines, and upper odd fourth digit lines are coupled through additional contact structures within upper odd first digit line exit regions of the upper memory array structure to the upper odd sense amplifiers.

7. The microelectronic device of claim 6, wherein:

the lower odd first digit lines and lower odd second digit lines are in a first array subregion;

the lower odd second digit lines and lower odd fourth digit lines are in a second array subregion;

the first array subregion and second array subregion are adjacent the lower odd first and second digit line exit regions;

the upper odd first digit lines and upper odd second digit lines are in a first array subregion;

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the upper odd second digit lines and upper odd fourth digit lines are in a second array subregion; and
the first array subregion and second array subregion are adjacent the upper odd first and second digit line exit regions.

8. The microelectronic device of claim 2, wherein:

each of the upper memory array structure and the lower memory array structure further comprises array subregions comprising first array subregions, second array subregions, third array subregions, and fourth array subregions;

the first array subregions and the second array subregions are adjacent first and second odd digit line exit regions in a first direction;

the third array subregions and the fourth array subregions are adjacent the first and second odd digit line exit regions in the first direction;

the first array subregions and the third array subregions are adjacent first and second odd word line exit regions in a second direction orthogonal to the first direction; and

the second array subregions and the fourth array subregions are adjacent the first and second odd word line exit regions in the second direction.

9. The microelectronic device of claim 8, further comprising:

electrically inactive word lines within the array subregions and horizontally proximate word line exit regions; and

digit line redistribution layer contact pads in the upper memory array structure are vertically above and laterally proximate at least some of the electrically inactive word lines.

10. The microelectronic device of claim 8, further comprising:

electrically inactive word lines within the array subregions and horizontally proximate word line exit regions; and

digit line redistribution layer contact pads in the upper memory array structure, at least some of the digit line redistribution layer contact pads vertically directly above and laterally proximate at least some of the electrically inactive word lines.

11. The microelectronic device of claim 2, wherein:

each of the upper memory array structure and the lower memory array structure further comprises:

first array subregions, second array subregions, third array subregions, and fourth array subregions;

the first array subregions and the second array subregions are adjacent first and second odd digit line exit regions in a first direction, and wherein the first array subregions and the second array subregions are each adjacent first and second even word line exit regions in a second direction orthogonal to the first direction;

the third array subregions and the fourth array subregions are adjacent first and second odd digit line exit regions in the first direction, and wherein the third array subregions and the fourth array subregions are each adjacent first and second even word line exit regions in the second direction;

the first array subregions and the third array subregions are each adjacent first and second even word line exit regions in the second direction orthogonal to the first direction; and

the second array subregions and the fourth array subregions are each adjacent first and second even word line exit regions in the second direction.

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12. The microelectronic device of claim 1, wherein the routing couples digit lines coupled to the memory cells of the upper memory array structure to the some of the sense amplifiers of the control logic structure.

13. The microelectronic device of claim 12, wherein:

the additional routing couples additional digit lines coupled to the additional memory cells of the lower memory array structure to the some other of the sense amplifiers of the control logic structure; and

path lengths of the routing between the digit lines and the some of the sense amplifiers are shorter than additional path lengths of the additional routing between the additional digit lines and the some other of the sense amplifiers.

14. The microelectronic device of claim 13, wherein the routing and the additional routing individually extend between the sense amplifier exit regions and digit line exit regions horizontally alternating with array regions including the memory cells and the additional memory cells within horizontal areas thereof.

15. The microelectronic device of claim 1, further comprising filled socket openings comprising dielectric material laterally bounded by and adjacent semiconductive material, the fill socket openings comprising:

first filled socket openings within vertical boundaries of the lower memory array structure and individually having a first lateral dimension;

second filled socket openings within vertical boundaries of the upper memory array structure and horizontally overlapping the first fill socket openings, the second filled socket openings individually having a second lateral dimension larger than the first lateral dimension; and

third filled socket openings within vertical boundaries of the control logic structure and horizontally overlapping the first fill socket openings and the second filled socket openings, third filled socket openings individually having a third lateral dimension larger than the second lateral dimension.

16. The microelectronic device of claim 15, wherein:
the first filled socket openings further comprise digit line contacts within horizontal areas thereof; and
the second filled socket openings further comprise additional digit line contacts within horizontal areas thereof, a quantity of the additional digit line contacts greater than a quantity of the digit line contacts.

17. The microelectronic device of claim 16, wherein:

the digit line contacts physically contact digit lines in electrical communication with the additional memory cells of the lower memory array structure;

some of the additional digit line contacts physically contact the digit line contacts; and

some other of the additional digit line contacts physically contact additional digit lines in electrical communication with the memory cells of the upper memory array structure.

18. The microelectronic device of claim 1, wherein the control logic structure further comprises additional control logic devices outside of horizontal areas of the sense amplifiers and comprising complementary metal-oxide-semiconductor (CMOS) circuitry.

19. A microelectronic device, comprising:

a first memory array structure comprising:

first array regions individually including first memory cells;

first digit lines coupled to the first memory cells of the first array regions and extending in a first direction,

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at least some of the first digit lines terminating within digit line exit regions alternating with the first array regions in the first direction; and

first word lines coupled to the first memory cells of the first array regions and extending in a second direction orthogonal to the first direction, at least some of the first word lines terminating within word line exit regions alternating with the first array regions in the second direction;

a second memory array structure vertically overlying the first memory array structure and comprising:

- second array regions individually including second memory cells;
- second digit lines coupled to the second memory cells of the second array regions and extending in the first direction, at least some of the second digit lines terminating within the digit line exit regions; and
- second word lines coupled to the second memory cells of the second array regions and extending in the second direction, at least some of the second word lines terminating within the word line exit regions; and

a control logic structure vertically overlying the second memory array structure and comprising:

- first sense amplifiers coupled to the first digit lines;
- second sense amplifiers coupled to the second digit lines;
- first sub-word line drivers coupled to the first word lines; and
- second sub-word line drivers coupled to the second word lines.

20. The microelectronic device of claim **19**, wherein: the first sense amplifiers horizontally neighbor sense amplifier exit regions in the first direction; and the second sense amplifiers horizontally neighbor the first sense amplifiers in the first direction, the first sense amplifiers horizontally interposed between the second sense amplifiers and the sense amplifier exit regions.

21. The microelectronic device of claim **20**, further comprising:

- first digit lines contact structures within the digit line exit regions and coupled to the first digit lines;
- second digit lines contact structures within the digit line exit regions and coupled to the second digit lines;
- first routing structures coupled and extending between the first digit lines contact structures and the first sense amplifiers; and
- second routing structures coupled and extending between the second digit lines contact structures and the second sense amplifiers.

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22. The microelectronic device of claim **21**, wherein: the first routing structures horizontally extend between the digit line exit regions and the sense amplifier exit regions; and the second routing structures horizontally extend between the digit line exit regions and the sense amplifier exit regions.

23. An electronic system, comprising:

- an input device;
- an output device;
- a processor device operably coupled to the input device and the output device; and
- a memory device operably coupled to the processor device and comprising at least one microelectronic device structure comprising:
 - a control logic device structure comprising:
 - sense amplifiers horizontally neighboring sense amplifier exit regions; and
 - sub-word line drivers horizontally offset from the sense amplifiers;
 - a first microelectronic device structure vertically underlying the control logic device structure and including memory cells coupled to some of the sense amplifiers by way of conductive structures extending from some of the memory cells and through the sense amplifier exit regions; and
 - a second microelectronic device structure vertically interposed between the first microelectronic device structure and the control logic device structure, the second microelectronic device structure including additional memory cells coupled to some other of the sense amplifiers by way of additional conductive structures extending from the additional memory cells and through sense amplifier exit regions.

24. The electronic system of claim **23**, further comprising: first dielectric-filled sockets in the first microelectronic device structure and individually having a first lateral dimension;

- second dielectric-filled sockets in the second microelectronic device structure and individually having a second lateral dimension larger than the first lateral dimension; and
- third dielectric-filled sockets in the control logic device structure and individually having a third lateral dimension larger than the second lateral dimension.

25. The electronic system of claim **23**, wherein the memory device comprises a DRAM device.

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